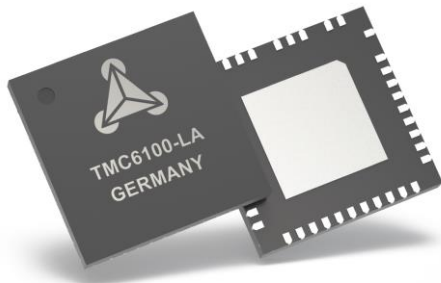


# TMC6100 DATASHEET

*Universal high voltage BLDC/PMSM/Servo MOSFET 3-halfbridge gate-driver with up to 1.5A drive current. Tiny QFN package with high creeping distance. External MOSFETs for up to 100A current.*



## APPLICATIONS

PMSM FOC drives and BLDC motors  
Industrial Drives  
Factory Automation  
Lab Automation  
Robotics  
CNC machines  
Textile Machines  
Pumps  
Surveillance Cameras  
Home Automation  
Printers

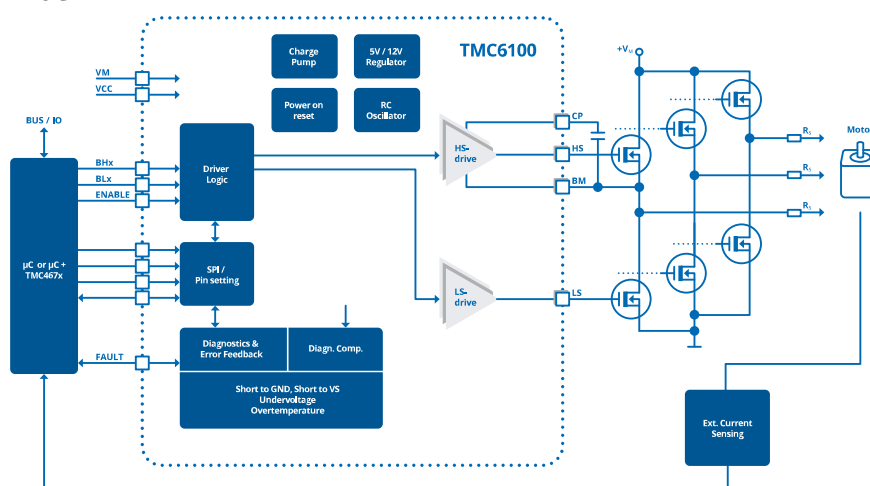
## FEATURES AND BENEFITS

**3-phase** motors up to 100A coil current (external MOSFETs)  
**Voltage Range** 8 ... 60V DC  
**Gate Drive Programmable** 0.5A / 1A / 1.5A  
**Full Protection and Diagnostics** via SPI interface  
**Gate Off Drive** with 1Ω (LS) / 1.3Ω (HS) safe hold off resistance  
**SPI & Stand-Alone** operation  
**Charge Pump** for 100% Duty Cycle operation  
**Optional BBM** break-before-make logic for single line control  
**Programmable Short and Overload** current threshold and retry  
**Programmable Control Interface** with 3-line or 6-line drive  
**Full Protection & Diagnostics**  
**Compact Size** 7x7mm<sup>2</sup> QFN package  
**Double Pin Distance** for safe operation at high voltage

## DESCRIPTION

The TMC6100 is a high-power gate-driver for PMSM servo or BLDC motors. Using six external MOSFETs it controls motors from Watt to Kilowatt. Software controlled drive strength allows in-system EME optimization. Programmable safety features like short detection and overtemperature thresholds together with an SPI interface for diagnostics allow robust and reliable designs. With the TMC6100, a minimum number of external components is required to build a rugged drive with full protection and diagnostics.

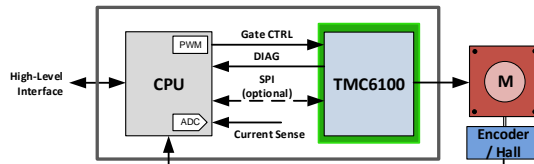
## BLOCK DIAGRAM



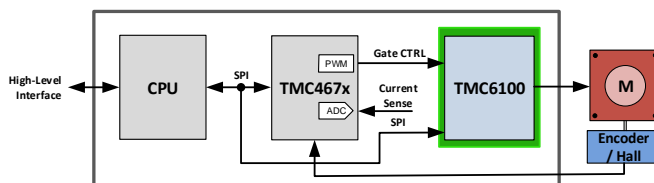
## APPLICATION EXAMPLES: PMSM AND BLDC MOTORS

The TMC6100 is a compact driver IC for PMSM drivers. Its special package has sufficient creeping distance, even for voltages of 48V. On the control side, it mates with sophisticated FOC TMC467x and TMC867x family controller chips, or with any microcontroller. Its versatile interface matches simple BLDC drives with minimum requirements on the  $\mu$ C PWM, as well as advanced PMSM control algorithms. The small form factor of the TMC6100 keeps costs down and allows for miniaturized layouts. Extensive support at the chip, board, and software levels enables rapid design cycles and fast time-to-market with competitive products. High integration and reliability deliver cost savings in related systems such as power supplies and cooling.

### MINIATURIZED CPU BASED DESIGN FOR BLDC OR PMSM



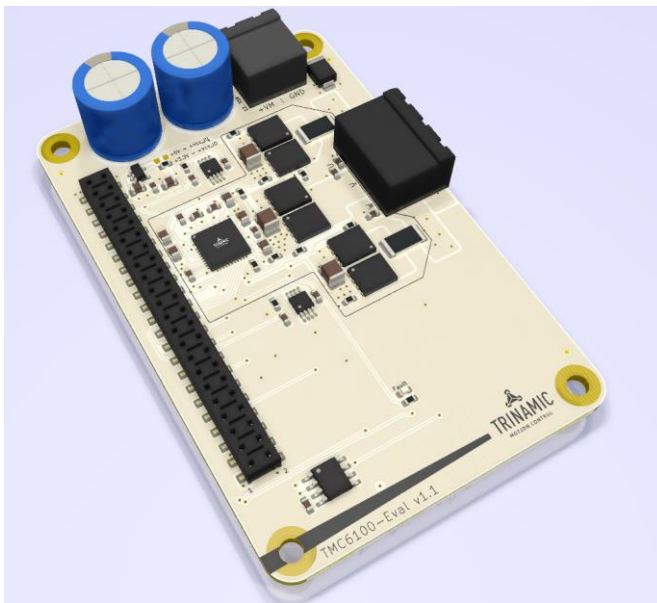
### HIGH PERFORMANCE FOC SERVO DESIGN FOR PMSM



A CPU with internal BLDC or sine wave PWM unit drives the gate control lines based on encoder or hall sensor feedback. External current sensing is required, either using simple Op AMPs for foot point sensing, or series shunt amplifiers. Use of SPI is not required, unless more sophisticated diagnostics is desired.

When using one of the TRINAMIC FOC controllers, the CPU is completely offloaded from time-intensive regulation loop tasks, and software design shrinks to initialization and target parameter setting. The TMC6100 optimally complements a TMC467x family controller.

The TMC6100-EVAL is part of TRINAMIC's universal evaluation board system which provides a convenient handling of the hardware as well as a user-friendly software tool for evaluation. The TMC6100 evaluation board system consists of three parts: LANDUNGSBRÜCKE (base board), ESELSBRÜCKE (connector board including several test points), and TMC6100-EVAL, plus a TMC4671-EVAL FOC controller.



### ORDER CODES

Order code	PN	Description	Size [mm <sup>2</sup> ]
TMC6100-TA	00-0201	Three phase gate-driver for external MOSFETs; QFN 7x7	7 x 7
TMC6100-TA-T	00-0201-T	-T denotes tape on reel packed devices	
TMC6100-EVAL	40-0197	Evaluation board for TMC6100.	85 x 80
LANDUNGSBRÜCKE	40-0167	Baseboard for TMC6100-EVAL and further boards.	85 x 55
ESELSBRÜCKE	40-0098	Connector board for plug-in evaluation board system.	61 x 38

# Table of Contents

<b>1</b>	<b>PRINCIPLES OF OPERATION</b> .....	<b>4</b>	8.1	USING THE INTERNAL CLOCK	29
1.1	CONTROL INTERFACES	6	8.2	USING AN EXTERNAL CLOCK	29
<b>2</b>	<b>PIN ASSIGNMENTS</b> .....	<b>7</b>	<b>9</b>	<b>ABSOLUTE MAXIMUM RATINGS</b> .....	<b>30</b>
2.1	PACKAGE OUTLINE	7	<b>10</b>	<b>ELECTRICAL CHARACTERISTICS</b> .....	<b>30</b>
2.2	SIGNAL DESCRIPTIONS	7	10.1	OPERATIONAL RANGE	30
<b>3</b>	<b>SAMPLE CIRCUITS</b> .....	<b>10</b>	10.2	DC AND TIMING CHARACTERISTICS	31
3.1	STANDARD APPLICATION CIRCUIT	10	10.3	THERMAL CHARACTERISTICS	34
3.2	EXTERNAL GATE VOLTAGE REGULATOR	11	<b>11</b>	<b>LAYOUT CONSIDERATIONS</b> .....	<b>35</b>
3.3	ZERO STANDBY CURRENT	12	11.1	EXPOSED DIE PAD	35
3.4	MOSFETS AND SLOPE CONTROL	13	11.2	WIRING GND	35
3.5	TUNING THE MOSFET BRIDGE	15	11.3	WIRING BRIDGE SUPPLY	35
<b>4</b>	<b>SPI INTERFACE</b> .....	<b>18</b>	11.4	SUPPLY FILTERING	35
4.1	SPI DATAGRAM STRUCTURE	18	11.5	LAYOUT EXAMPLE	36
4.2	SPI SIGNALS	19	<b>12</b>	<b>PACKAGE MECHANICAL DATA</b> .....	<b>38</b>
4.3	TIMING	20	12.1	DIMENSIONAL DRAWINGS QFN7x7-EP	38
<b>5</b>	<b>REGISTER MAPPING</b> .....	<b>21</b>	12.2	PACKAGE CODES	39
5.1	GENERAL CONFIGURATION REGISTERS	22	<b>13</b>	<b>DISCLAIMER</b> .....	<b>40</b>
<b>6</b>	<b>DIAGNOSTICS AND PROTECTION</b> .....	<b>27</b>	<b>14</b>	<b>ESD SENSITIVE DEVICE</b> .....	<b>40</b>
6.1	TEMPERATURE SENSORS	27	<b>15</b>	<b>DESIGNED FOR SUSTAINABILITY</b> .....	<b>40</b>
6.2	SHORT PROTECTION	27	<b>16</b>	<b>TABLE OF FIGURES</b> .....	<b>41</b>
<b>7</b>	<b>EXTERNAL RESET</b> .....	<b>29</b>	<b>17</b>	<b>REVISION HISTORY</b> .....	<b>41</b>
<b>8</b>	<b>CLOCK OSCILLATOR AND INPUT</b> .....	<b>29</b>			

# 1 Principles of Operation

The TMC6100 is a MOSFET gate driver for three phase PMSM and BLDC motors. Ideally suited for applications in the range of 12V to 48V, it supports motor power ratings from 1 Watt to 1kW. It complements with TRINAMICs TMC467x & TMC867x families of three phase motor controller ICs. Internal break-before-make timing is provided for the ease-of-use in combination with simple microcontrollers for PWM generation. A complete set of protection and diagnostic functions makes the power stage more rugged than a discrete setup.

## THE TMC6100 OFFERS TWO BASIC MODES OF OPERATION:

### MODE 1: Stand-alone driver with pin configuration

Enable this mode by tying low pin SPE. The interface pins allow a number of different settings for BBM generation.

### MODE 2: SPI controlled

This mode allows detailed control over the protection, diagnostic and control features, e.g. for tuning overcurrent detection. Enable this mode by tying high pin SPE.

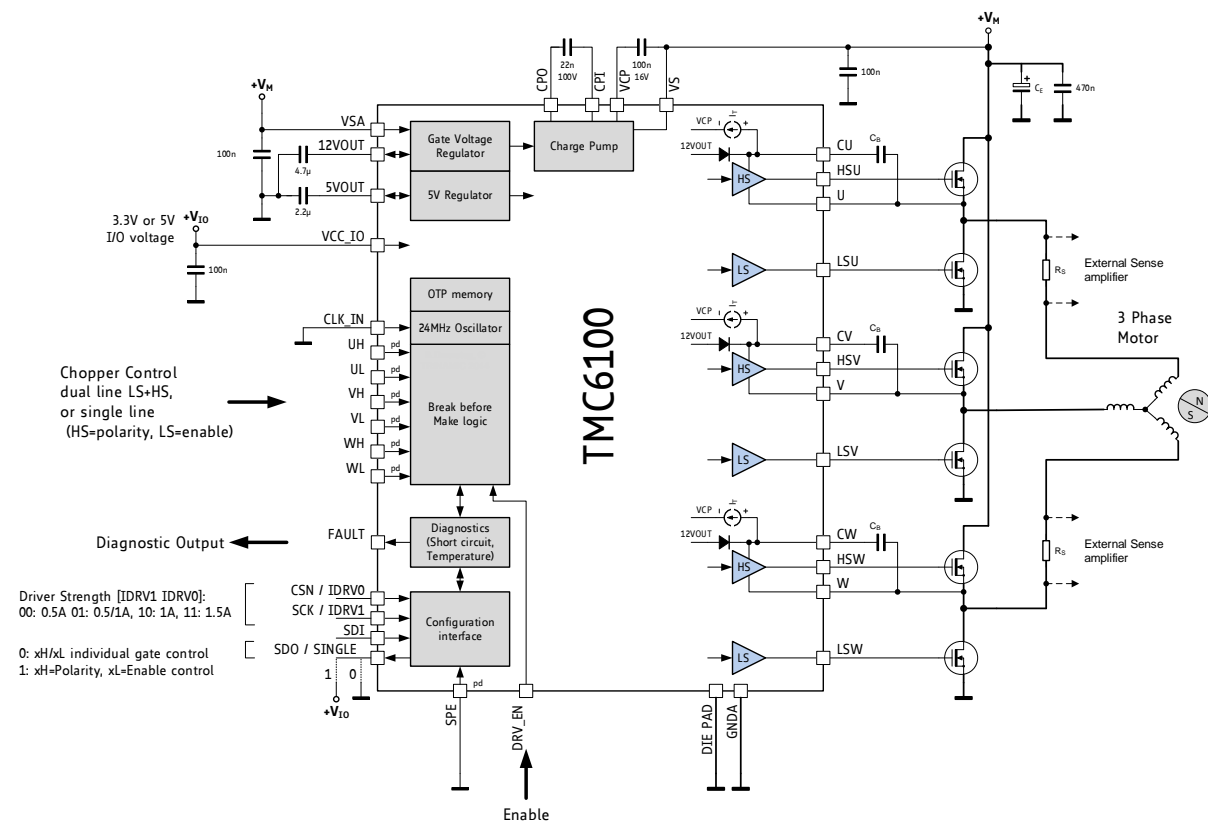


Figure 1.1 Standalone application

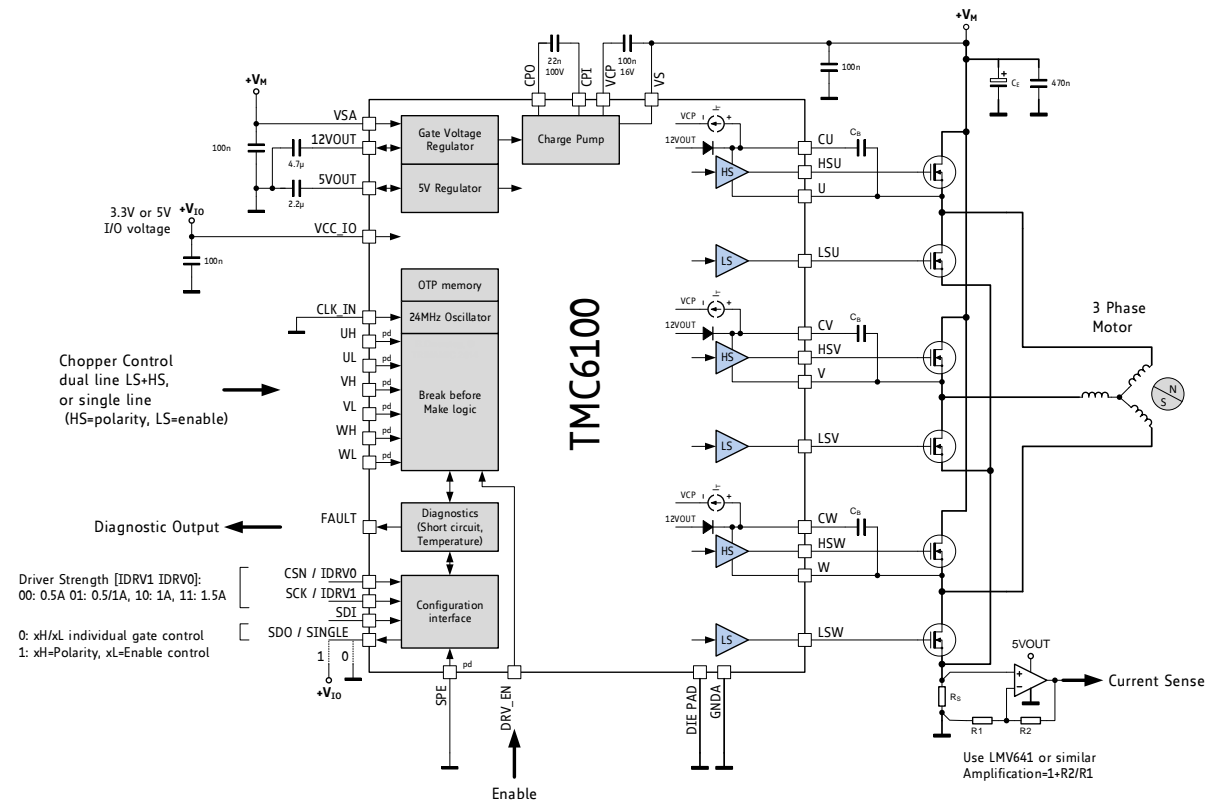


Figure 1.2 Standalone application using single shunt current sensing

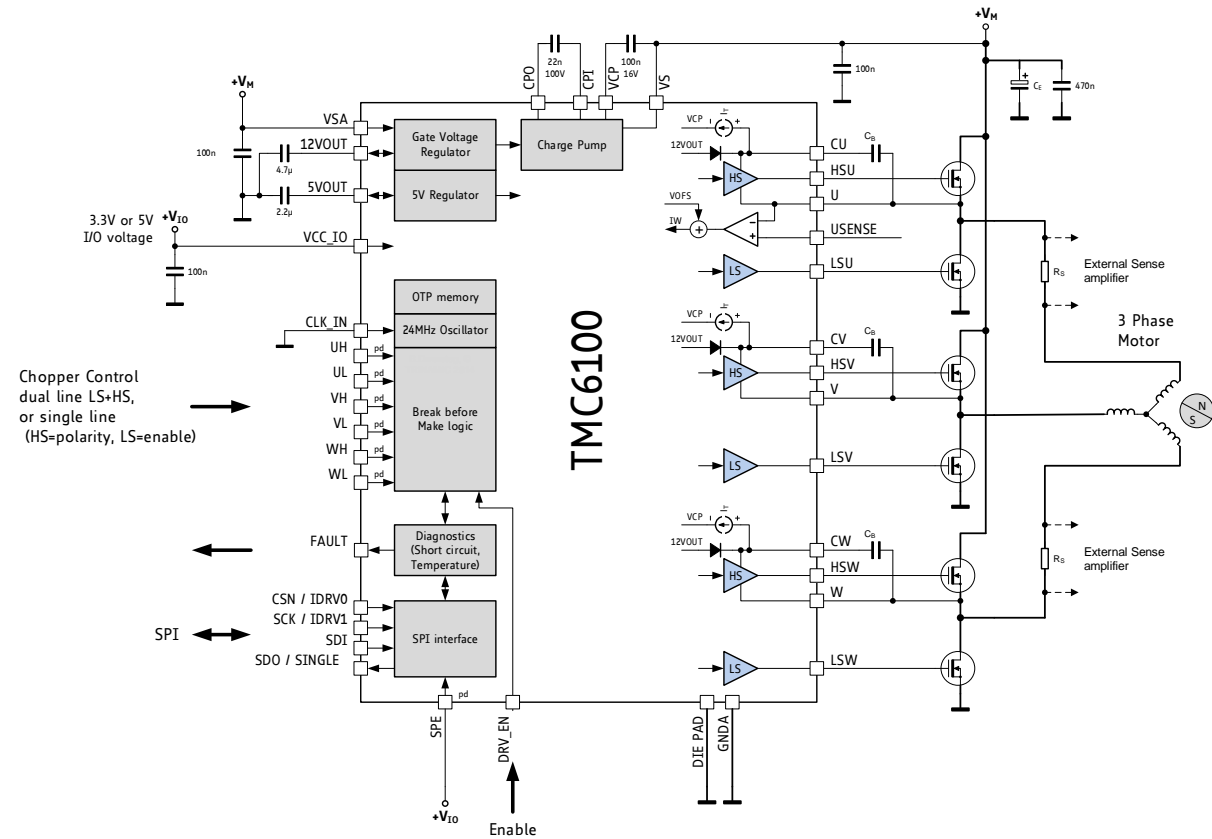


Figure 1.3 SPI mode configuration

## 1.1 Control Interfaces

The TMC6100 supports six control lines for the MOSFET drivers. High-side and low-side outputs can be individually controlled, or by an individual enable pin plus polarity pin, using internal BBM circuitry. An SPI interface or standalone configuration is supported.

### 1.1.1 Standalone Configuration

Standalone configuration covers the most important settings like driver current and current amplifier amplification factor and the selection of internal or external BBM operation using four pins. Additional settings like BBM time and sensitivity of short detection can be modified using pre-programming via OTP memory, e.g. via an initial programming during product testing. This way, the driver can be fully operated and all protection mechanisms are in place. The fault output signals any critical driver error. It becomes cleared by disabling / re-enabling the driver.

However, no advanced debugging is possible, like individual testing of failure mechanisms or setting a more sensitive temperature threshold.

#### *Hint*

Standalone configuration is recommended for low-cost applications with small motors (e.g. motor current up to 10A RMS), where advanced debugging is not required or not possible. In case a sensitive overtemperature threshold must be set, the SPI interface should be used.

### 1.1.2 SPI Interface

The SPI interface is a bit-serial interface synchronous to a bus clock. For every bit sent from the bus master to the bus slave another bit is sent simultaneously from the slave to the master. Communication between an SPI master and the TMC6100 slave always consists of sending one 40-bit command word and receiving one 40-bit status word.

The SPI command rate typically is a few commands for initialization or for diagnostic feedback.

#### *Attention*

When operating in SPI mode, set drive mode (single line or individual control signals) first. For safety reasons, the driver starts up in single line mode. Note, that this setting will prevent operation if a controller operates the IC using individual control signals. Therefore, initialize the control mode first.

## 2 Pin Assignments

### 2.1 Package Outline

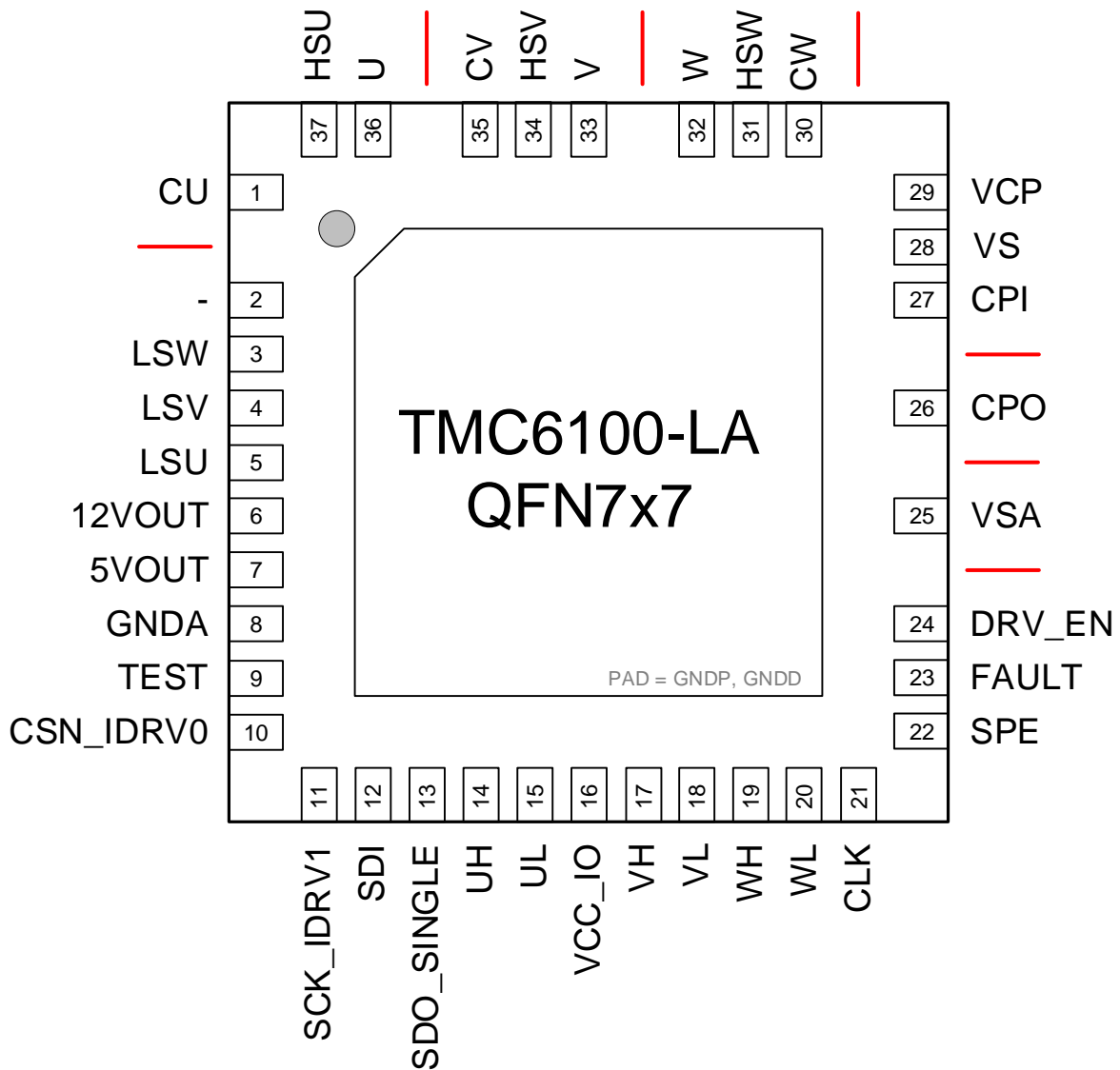


Figure 2.1 TMC6100-LA pinning QFN 37 special (7x7mm<sup>2</sup>)

### 2.2 Signal Descriptions

Pin	QFN	Type	Function
CU	1		Bootstrap capacitor positive connection. Tie to U terminal using 470nF to 1µF, 16V or 25V ceramic capacitor.
-	2	N.C.	Unused pin (may be tied to GND)
LSW	3		Low side gate driver output.
LSV	4		Low side gate driver output.
LSU	5		Low side gate driver output.

Pin	QFN	Type	Function
12VOUT	6		Output of internal 11.5V gate voltage regulator and supply pin of low side gate drivers. Attach 2.2 $\mu$ F to 22 $\mu$ F ceramic capacitor to GND plane near to pin for best performance. Use at least 5-10 times more capacity than for bootstrap capacitors. In case an external gate voltage supply is available, tie VSA and 12VOUT to the external supply.
5VOUT	7		Output of internal 5V regulator. Attach 2.2 $\mu$ F to 10 $\mu$ F ceramic capacitor to GNDA near to pin for best performance.
GNDA	8		Analog GND. Connect to GND plane near pin.
TEST	9	AI	leave open
CSN_IDRV0	10	DI	SPI chip select input (negative active) (SPE=1) or Configuration input for gate driver current LSB (SPE=0)
SCK_IDRV1	11	DI	SPI serial clock input (SPE=1) or Configuration input for gate driver current MSB (SPE=0)
SDI	12	DI	SPI data input
SDO_SINGLE	13	DIO	SPI data output (tristate) (SPE=1) or Configuration input for internal bridge control mode (0: dual line, 1: xH=phase polarity, xL=phase enable) (SPE=0)
UH	14	DI (pd)	High side control input (or bridge polarity in single mode)
UL	15	DI (pd)	Low side control input (or bridge enable in single mode)
VCC_IO	16		3.3V to 5V IO supply voltage for all digital pins.
VH	17	DI (pd)	High side control input (or bridge polarity in single mode)
VL	18	DI (pd)	Low side control input (or bridge enable in single mode)
WH	19	DI (pd)	High side control input (or bridge polarity in single mode)
WL	20	DI (pd)	Low side control input (or bridge enable in single mode)
CLK	21	DI	CLK input. Tie to GND using short wire for internal clock or supply external clock. Internal clock-fail over circuit protects against loss of external clock signal.
SPE	22	DI (pd)	Mode selection input. When tied low, the chip is in standalone mode and SPI pins have their configuration pin functions. When tied high, the SPI interface is enabled. Integrated pull down resistor.
FAULT	23	DO	Diagnostics output. High upon driver error condition. Clear by cycling EN.
DRV_EN	24	DI	Positive active enable input. The power stage becomes switched off (all motor outputs floating) when this pin becomes driven to a low level. Cycle low to clear FAULT.
VSA	25		Analog supply voltage for 11.5V and 5V regulator. Normally tied to VS. Provide a 100nF filtering capacitor to GND.
CPO	26		Charge pump capacitor output.
CPI	27		Charge pump capacitor input. Tie to CPO using 22nF 100V capacitor. In case ringing of the power supply leads to considerable supply ripple, add a 10-220 $\Omega$ series resistor.
VS	28		Motor supply voltage. Provide filtering capacity near pin with short loop to GND plane. Must be tied to the positive bridge supply voltage. Severe ringing must be avoided.
VCP	29		Charge pump voltage. Tie to VS using 100nF capacitor.



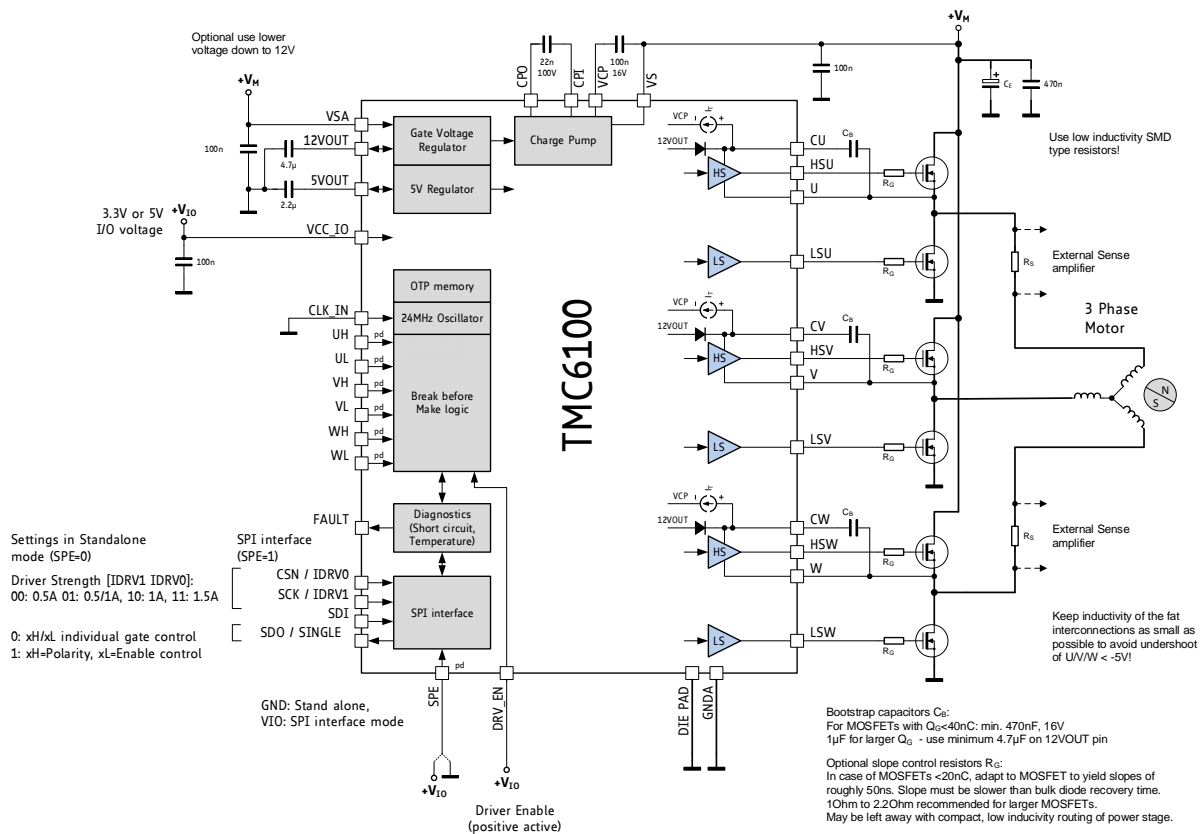
Pin	QFN	Type	Function
CW	30		Bootstrap capacitor positive connection. Tie to W terminal using 470nF to 1 $\mu$ F, 16V or 25V ceramic capacitor.
HSW	31		High side gate driver output.
W	32		Bridge center and bootstrap capacitor negative connection. Connect to source pin of HS-MOSFET.
V	33		Bridge center and bootstrap capacitor negative connection. Connect to source pin of HS-MOSFET.
HSV	34		High side gate driver output.
CV	35		Bootstrap capacitor positive connection. Tie to V terminal using 470nF to 1 $\mu$ F, 16V or 25V ceramic capacitor.
U	36		Bridge center and bootstrap capacitor negative connection. Connect to source pin of HS-MOSFET.
HSU	37		High side gate driver output.
Exposed die pad	-		Connect the exposed die pad to a GND plane. Provide as many as possible vias for heat transfer to GND plane. Serves as GND pin for the low side gate drivers and for digital logic. Ensure low loop inductivity to bridge GND.

\*(pd) denominates a pin with pulldown resistor

## 3 Sample Circuits

The following sample circuits show the required external components in different operation and supply modes. The connection of the external current amplifier, bus interface and further digital signals are left out for clarity.

### 3.1 Standard Application Circuit



**Figure 3.1** Standard application circuit

The standard application circuit uses a minimum set of additional components. Six MOSFETs are selected for the desired current, voltage and package type. Two or three sense resistors are matched to the maximum motor coil current, and to the desired external current amplifier output swing and amplification setting. Use low ESR capacitors for filtering the power supply. A minimum capacity of 100μF per ampere of coil current near to the power bridge is recommended for keeping power supply ripple low. The capacitors need to cope with the current ripple caused by chopper operation. Current ripple in the supply capacitors also depends on the power supply internal resistance and cable length. Supply VCC\_IO from 5VOUT, or from an external source, e.g. a 3.3V regulator. In order to minimize linear voltage regulator power dissipation of the internal 5V and 11.5V voltage regulators in applications where VM is high, a different (lower) supply voltage should be used for VSA, when available (see chapter 3.2).

#### Important layout hints

Place all filter capacitors as close as possible to the power MOSFETs. Place the TMC6100 near to the MOSFETs and use short interconnection lines in order to minimize parasitic trace inductance. Use a solid common GND for all GND and GNDA connections. Connect 5VOUT filtering capacitor directly to 5VOUT and GNDA pin. See layout hints for more details. Low ESR electrolytic capacitors are recommended for VS filtering.

**Attention**

In case VSA is supplied by a different voltage source, make sure that VSA does not drop out during motor operation. The motor driver should be disabled in case VSA becomes switched off before VS. Hard switching edges on VSA might result in bridge cross-conduction otherwise. It is safest to derive VSA voltage from VS supply. VS power slope also should be limited to 0.5V/ $\mu$ s or less.

**Attention**

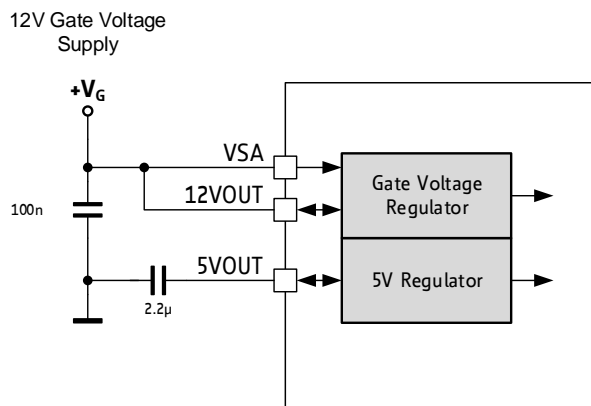
Make sure, that VCC\_IO does not drop out during operation of the motor. Disable the drive when a falling supply voltage is detected. It is safest to use the same source for VCC\_IO as for the controller driving the motor.

**Hint**

VCC\_IO undervoltage detection disables the MOSFET drivers. This will avoid motor overcurrent due to instable input levels during power-up / power-down for most cases. However, it is best practice to disable the motor prior to switching off power supply, and to make sure, that the motor power supply does come up without or not remain with missing VCC\_IO supply.

## 3.2 External Gate Voltage Regulator

At high supply voltages like 48V, the internal gate voltage regulator and the internal 5V regulator have considerable power dissipation, especially with high MOSFET gate charges or high chopper frequency. A good thermal coupling of the heat slug to the system PCB GND plane is required to dissipate heat. Still, the thermal thresholds will be lowered significantly by self-heating. To reduce power dissipation, supply an external gate driver voltage to the TMC6100. Figure 3.2 shows the required connection. The internal gate voltage regulator becomes disabled in this constellation. 12V  $\pm$ 1V is recommended for best results.



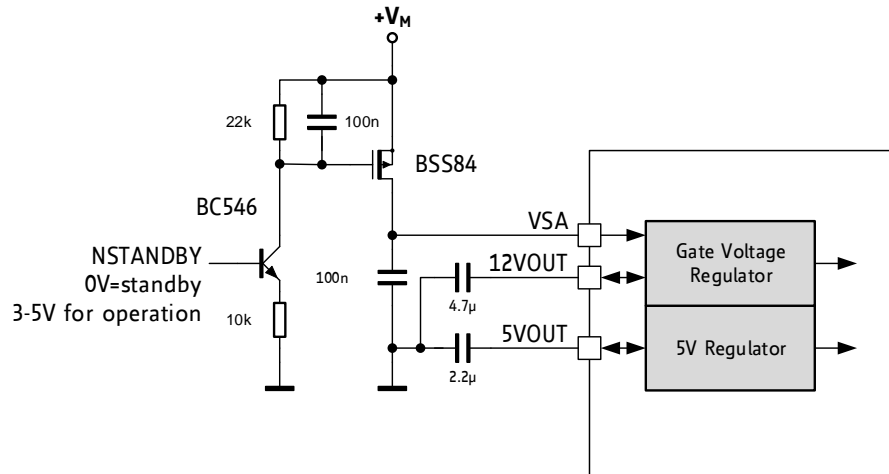
**Figure 3.2 External gate voltage supply**

**Hint**

With MOSFETs above 50nC of total gate charge or chopper frequency >40kHz, it is recommended to use a VSA supply not higher than 40V in order to keep reasonable power dissipation.

### 3.3 Zero Standby Current

Battery powered applications often require low current standby, while keeping the supply switched on. The TMC6100 can support these applications by completely powering down the control side, VSA, and with this also the charge pump and 5V supply. See Figure 3.3 for an example using a P-MOSFET as high-side switch. Gate charge / discharge is limited to avoid too steep slopes and excess current. VCC\_IO may remain active during standby operation. Make sure that the motor becomes disabled before switching off the power supply!



**Figure 3.3 Standby Switch**

#### Hint

Realize zero standby current by switching off VSA in standby mode. VCC\_IO may remain active. Ensure a slope-controlled power-up of  $1V/\mu s$  or less to avoid excess current into VSA.

#### Attention

Test your circuit thoroughly in order to ensure a safe and clean power-up and standby power-up and power-down event! When powering down the control side of the MOSFET drivers, MOSFET gate-off is only ensured by high-resistive resistors within the TMC6100. This makes the circuit more susceptible to injection of charge from MOSFET drain to gate, e.g. to high supply voltage slopes. Any spurious cross-conduction could lead to destructive currents through the power MOSFETs.

### 3.4 MOSFETs and Slope Control

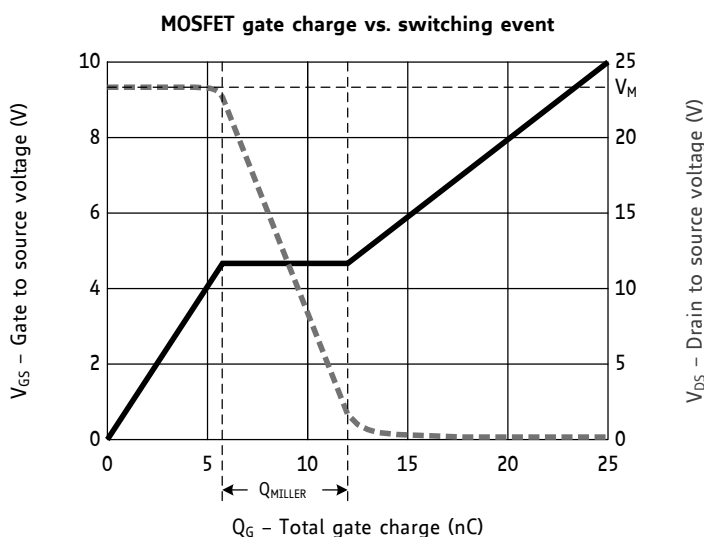
The selection of power MOSFETs depends on a number of factors, like package size, on-resistance, voltage rating and supplier. It is not true, that larger, lower RDSon MOSFETs will always be better, as a larger device also has higher capacitances and may add more ringing in trace inductance and power dissipation in the gate drive circuitry. Adapt the MOSFETs to the required motor voltage (adding 5-10V of reserve to the peak supply voltage) and to the desired maximum current, in a way that resistive power dissipation still is low for the chosen MOSFET package. The TMC6100 drives the MOSFET gates with roughly 10V, so normal, 10V specified types are sufficient. Logic level FETs (4.5V specified RDSon) will also work but may be more critical with regard to bridge cross-conduction due to lower  $V_{GS(th)}$ .

The gate-drive current and MOSFET gate resistors  $R_G$  (optional) should basically be adapted to the MOSFET gate-drain charge (Miller charge) in order to yield reasonable slope times. Figure 3.4 shows the influence of the Miller charge on the switching event. Figure 3.5 additionally shows the switching events in different load situations (load pulling the output up or down), and the required bridge brake-before-make time.

The following table shall serve as a thumb rule for programming the MOSFET driver current (*DRVSTRENGTH* setting) and the selection of gate resistors:

MOSFET MILLER CHARGE VS. <i>DRVSTRENGTH</i> AND $R_G$		
Miller Charge [nC] (typ.)	<i>DRVSTRENGTH</i> setting	Value of $R_G$ [ $\Omega$ ]
<10	0 or 1	$\leq 10$ (recommended)
10...20	0 to 2	$\leq 5$ (optional)
20...80	1 to 3	$\leq 2.5$ (optional)
>80	3	$\leq 1$ (optional)

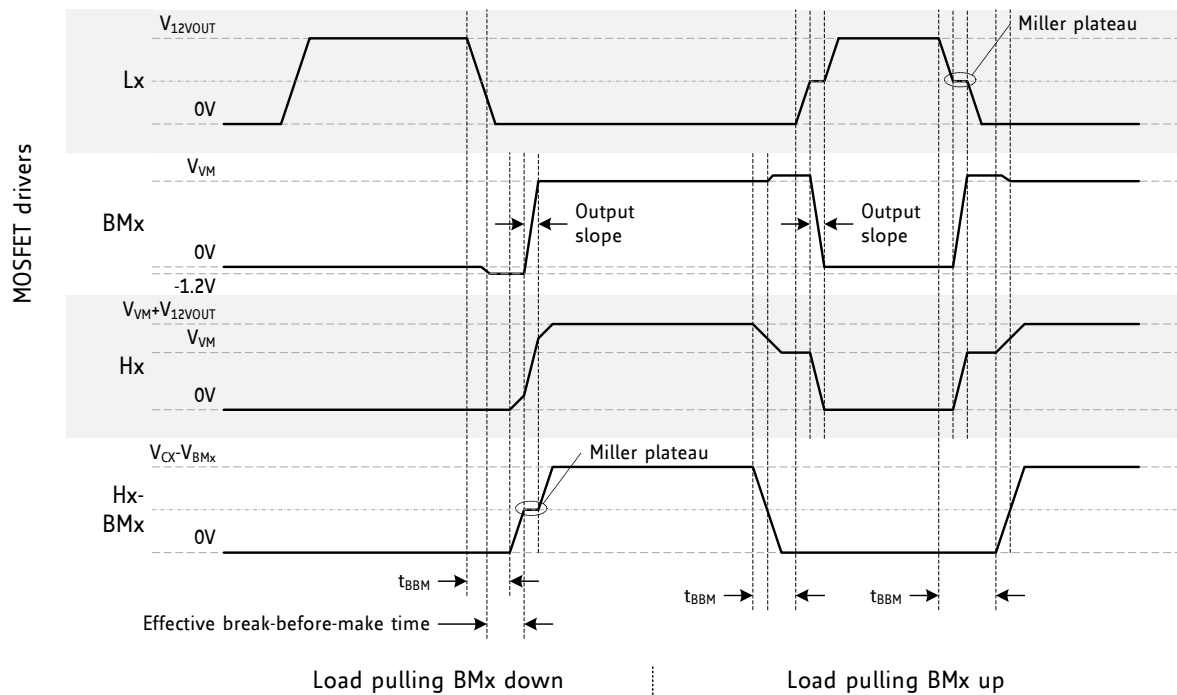
The TMC6100 provides increased gate-off drive current to avoid bridge cross-conduction induced by high  $dV/dt$ . This protection will be less efficient with gate resistors exceeding the values given in the table. For larger values of  $R_G$ , a parallel diode may be required to ensure keeping the MOSFET safely off during switching events of the opposite MOSFET.



**Figure 3.4 Miller charge determines switching slope**

#### Hints

- Choose modern MOSFETs with fast and soft recovery bulk diode and low reverse recovery charge.
- A small, SMD MOSFET package allows compacter routing and reduces parasitic inductance effects.



**Figure 3.5 Slopes, Miller plateau and blank time (BMx=U V or W output)**

The following *DRV\_CONF* parameters allow adapting the driver to the MOSFET bridge:

Parameter	Description	Setting	Comment
<i>BBMCLKS</i>	Break-before-make time setting to ensure non-overlapping switching of high-side and low-side MOSFETs. Digital BBM time in clock cycles (typ. 42ns/CLK). <i>BBMCLKS</i> is used in combination with <i>singleline</i> =1. It is not applicable with individual LS and HS signals. Additionally, a minimum BBM time of 75ns is enforced by analog circuitry even with individual control signals. This prevents short-circuiting of the bridge	0...15	time[ns]≈ 42ns* <i>BBMCLKS</i>  <i>Ensure -30% headroom</i> <i>Reset Default: OTP 1..4</i> <i>4, when not programmed</i>
<i>DRV_STRENGTH</i>	Selection of gate driver current. Adapts the gate driver current to the gate charge of the external MOSFETs.	0...3	<i>Reset Default = 2 in SPI mode</i>

#### *DRV\_CONF* Parameters

Use the lowest gate driver strength setting *DRV\_STRENGTH* giving favorable switching slopes, before increasing the value of the gate series resistors. A slope time of nominal 40ns to 80ns is absolutely sufficient and will normally be covered by a Break-Before-Make time setting of 1 to 4 (4 is default). In case slower slopes have to be used, e.g. with large MOSFETs, ensure that the break-before-make time sufficiently covers the switching event, in order to avoid bridge cross conduction. The shortest break-before-make time, safely covering the switching event, gives best results. Add roughly 30% of reserve, to cover production stray of MOSFETs and driver.

### 3.5 Tuning the MOSFET Bridge

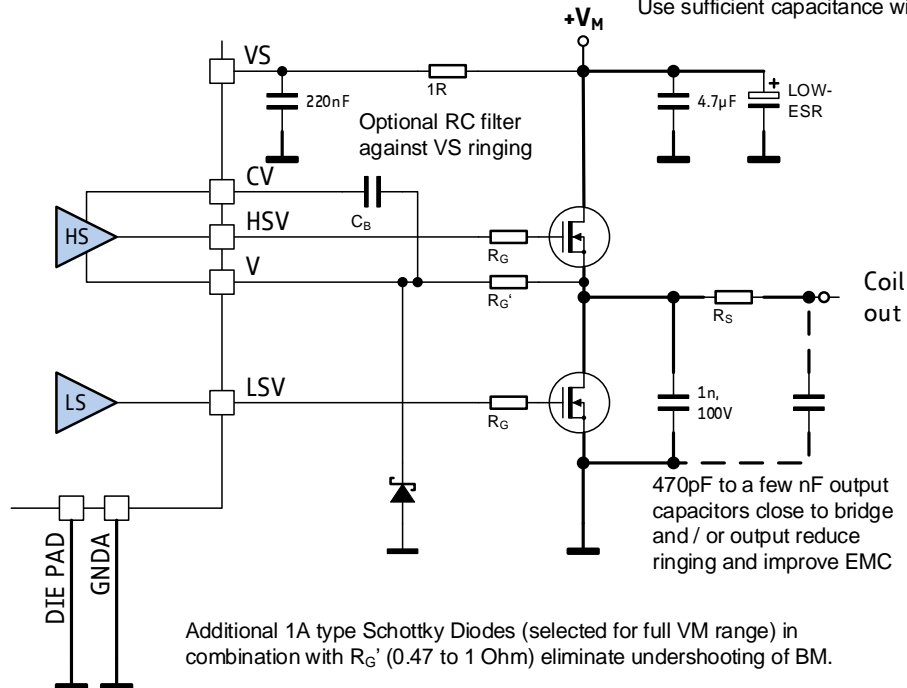
A clean switching event is favorable to ensure low power dissipation and good EMC behavior. Unsuitable layout or components endanger stable operation of the circuit. Therefore, it is important to understand the effect of parasitic trace inductivity and MOSFET reverse recovery.

Stray inductance in power routing will cause ringing whenever the opposite MOSFET is in diode conduction prior to switching on a low-side or high-side MOSFET. Diode conduction occurs during break-before make time whenever the load current is inverse to the following bridge polarity. The MOSFET bulk diode has a certain, type specific reverse recovery time and charge. This time typically is in the range of a few 10ns. During reverse recovery time, the bulk diode will cause high current flow across the bridge. This current is taken from the power supply filter capacitors (see thick lines Figure 3.6). Once the diode opens, parasitic inductance tries to keep the current flowing. A high, fast slope results and leads to ringing in all parasitic inductivities (see Figure 3.7). This may lead to bridge voltage undershooting the GND level as well as fast pulses on VS and all MOSFET connections. It must be ensured, that the driver IC does not see spikes on its BM pins to GND going below -5V. Severe VS ripple might overload the charge-pump circuitry. Measure the voltage directly at the driver pins to driver GND. The amount of undershooting depends on energy stored in parasitic inductivities from low side drain to low side source and via the sense resistor  $R_S$  to GND.

When using relatively small MOSFETs, a soft slope control requires a high gate series resistance. This endangers safe MOSFET switch off. Add additional diodes to ensure safe MOSFET off conditions with slow switch-on slopes (Figure 3.10).

$R_G$ : Reduce slope and protect the driver against ringing in the interconnections between MOSFET and driver

Place filtering capacitors near to the bridge to avoid severe overshooting and ringing. Use sufficient capacitance with regard to motor current.

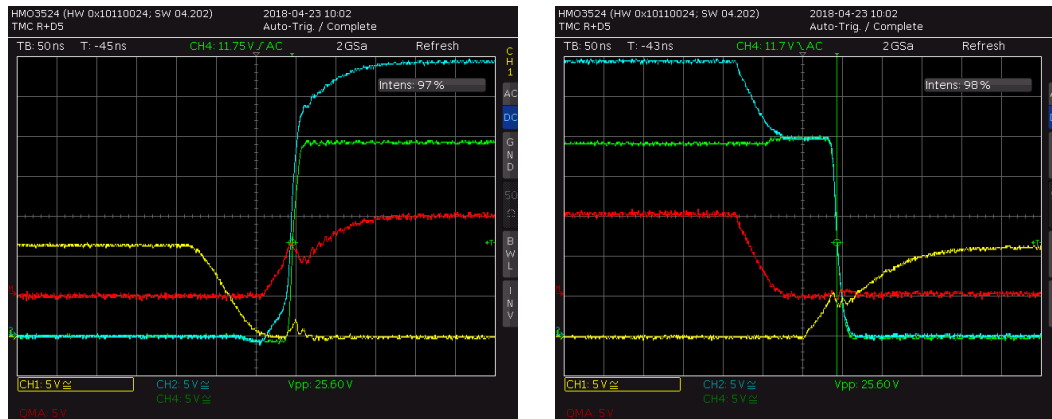


*Decide use and value of the additional components based on measurements of the actual circuit using the final layout!*

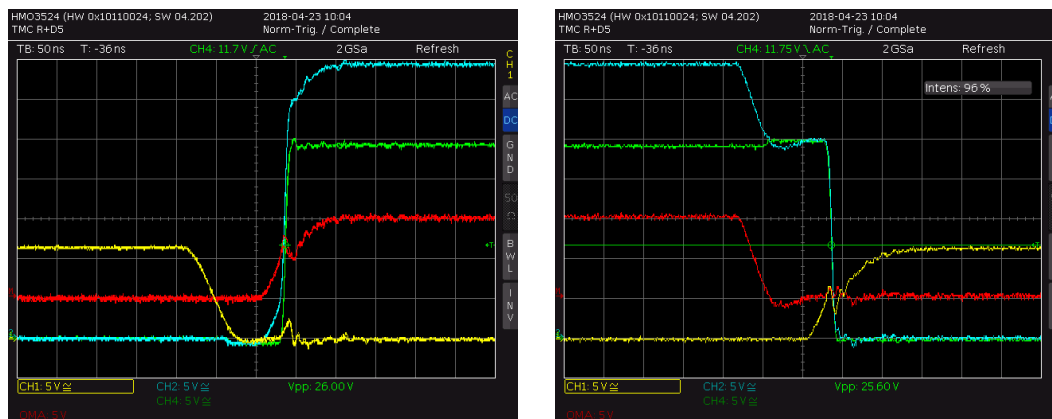
**Figure 3.6 Bridge protection options for power routing inductivity**

**ENSURE RELIABLE OPERATION**

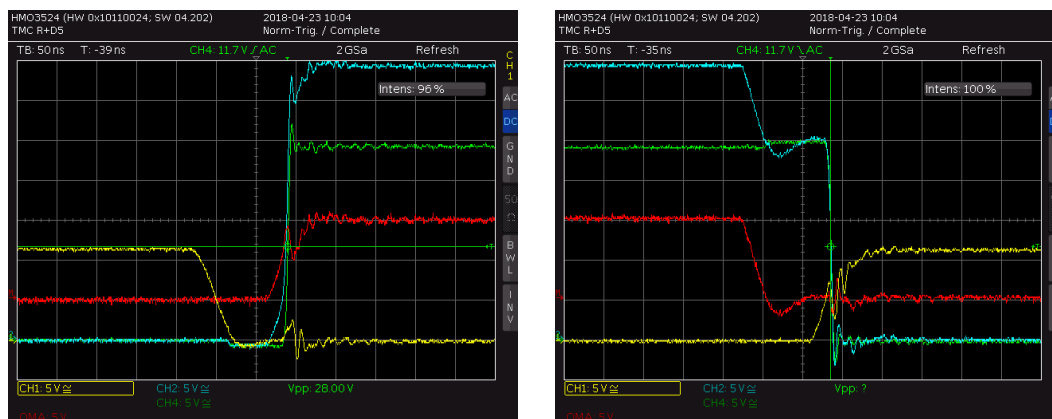
- Use SMD MOSFETs and short interconnections
- Provide sufficient power filtering capacity close to the bridge and close to VS pin
- Tune MOSFET switching slopes (measure switch-on event at MOSFET gate) to be slower than the MOSFET bulk diode reverse recovery time. This will reduce cross conduction.
- Add optional gate resistors close to MOSFET gate and output capacitors to ensure clean switching and reliable operation by minimizing ringing. Figure 3.6 shows the options plus some variations.
- Some MOSFETs eliminate reverse recovery charge by integrating a fast diode from source to drain.



**Figure 3.7 Ringing of output (green) and Gate voltages (yellow, blue) with DRVSTRENGTH=0**



**Figure 3.8 Ringing of output (green) and Gate voltages (yellow, blue) with DRVSTRENGTH=2**



**Figure 3.9 Ringing of output (green) and Gate voltages (yellow, blue) with DRVSTRENGTH=3**







### 4.1.2 Data Alignment

All data are right aligned. Some registers represent unsigned (positive) values, some represent integer values (signed) as two's complement numbers, single bits or groups of bits are represented as single bits respectively as integer groups.

## 4.2 SPI Signals

The SPI bus on the TMC6100 has four signals:

- SCK – bus clock input
- SDI – serial data input
- SDO – serial data output
- CSN – chip select input (active low)

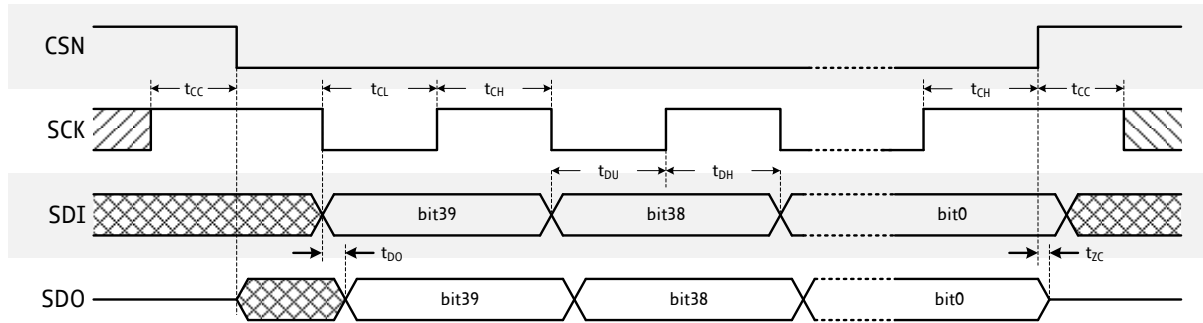
The slave is enabled for an SPI transaction by a low on the chip select input CSN. Bit transfer is synchronous to the bus clock SCK, with the slave latching the data from SDI on the rising edge of SCK and driving data to SDO following the falling edge. The most significant bit is sent first. A minimum of 40 SCK clock cycles is required for a bus transaction with the TMC6100.

The TMC6100 does not allow cascading of SPI slaves. Use individual CSN lines for each device.

CSN must be low during the whole bus transaction. When CSN goes high, the contents of the internal shift register are latched into the internal control register and recognized as a command from the master to the slave.

## 4.3 Timing

The SPI interface is synchronized to the internal system clock, which limits the SPI bus clock SCK to 1/4 of the system clock frequency. If the system clock is based on the on-chip oscillator, an additional 10% safety margin must be used to ensure reliable data transmission. All SPI inputs as well as the ENN input are internally filtered to avoid triggering on pulses shorter than 20ns. Figure 4.1 shows the timing parameters of an SPI bus transaction, and the table below specifies their values.



**Figure 4.1 SPI timing**

*Hint*

Usually this SPI timing is referred to as SPI MODE 3

SPI interface timing		AC-Characteristics				
		clock period: $t_{CLK}$				
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
SCK valid before or after change of CSN	$t_{CC}$		10			ns
CSN high time	$t_{CSH}$	*) Min time is for synchronous CLK with SCK high one $t_{CH}$ before CSN high only	$t_{CLK}^{*)}$	$>2t_{CLK}+10$		ns
SCK low time	$t_{CL}$	*) Min time is for synchronous CLK only	$t_{CLK}^{*)}$	$>t_{CLK}+10$		ns
SCK high time	$t_{CH}$	*) Min time is for synchronous CLK only	$t_{CLK}^{*)}$	$>t_{CLK}+10$		ns
SCK frequency using internal clock	$f_{SCK}$	assumes minimum OSC frequency			3.5	MHz
SCK frequency using external clock	$f_{SCK}$	assumes synchronous CLK			$f_{CLK}/6$	MHz
SDI setup time before rising edge of SCK	$t_{DU}$		10			ns
SDI hold time after rising edge of SCK	$t_{DH}$		10			ns
Data out valid time after falling SCK clock edge	$t_{DO}$	no capacitive load on SDO			$t_{CLK}+10$	ns
SDI, SCK and CSN filter delay time	$t_{FILT}$	rising and falling edge	12	20	30	ns

## 5 Register Mapping

This chapter gives an overview of the complete register set. Some of the registers bundling a number of single bits are detailed in extra tables. The functional practical application of the settings is detailed in dedicated chapters.

### Note

- All registers become reset to 0 upon power up, unless otherwise noted.
- Add 0x80 to the address Addr for a write access!

### NOTATION OF HEXADECIMAL AND BINARY NUMBERS

0x	precedes a hexadecimal number, e.g. 0x04
%	precedes a multi-bit binary number, e.g. %100

### NOTATION OF R/W FIELD

R	Read only
W	Write only
R/W	Read- and writable register
R+WC	Clear upon write back with '1'

### OVERVIEW REGISTER MAPPING

REGISTER	DESCRIPTION
General Configuration Registers	These registers contain <ul style="list-style-type: none"> <li>- global configuration</li> <li>- global status flags</li> <li>- interface configuration</li> <li>- driver configuration</li> <li>- OTP programming</li> </ul>

## 5.1 General Configuration Registers

GENERAL CONFIGURATION REGISTERS (0x00...0x0F)				
R/W	Addr	n	Register	Description / bit names
RW	0x00	17	GCONF	<b>Bit</b> <b>GCONF – Global configuration flags</b> 0 <i>disable</i> : Driver Disable 1: Disable driver (e.g. for Resetting of short condition)
				1 <i>singleline</i> : Interface mode ( <i>reset default = 1</i> ) 0: Individual signals L+H 1: H-Input is control signal, L-Input is Enable
				2 <i>faultdirect</i> 0: Fault output active when at least one bridge is shut down continuously due to overcurrent or overtemperature 1: Fault output shows each protective action of the overcurrent shutdown
				5:3 unused
				6 1: Normal operation - set upon write access for reduced power consumption
				7 <i>test_mode</i> 0: Normal operation 1: Enable analog test output on pin DRV_EN. <i>BBM_CLKS[1..0]</i> selects the function of DRV_EN: 0..2: T120, DAC, VDDH <i>Attention: Not for user, set to 0 for normal operation!</i>
				31:8 unused
				<b>Bit</b> <b>GSTAT – Global status flags</b> (Re-Write with '1' bit to clear respective flags, or cycle DRV_EN to clear all bits except for <i>reset</i> and <i>drv_otpw</i> ) <i>Attention: Switch off the affected MOSFET by its HS/LS input in order to clear a pending short condition. Just resetting the flag will not switch it on again.</i>
R+ WC	0x01	15	GSTAT	0 <i>reset</i> 1: Indicates that the IC has been reset. All registers have been cleared to reset values. <i>Attention: DRV_EN must be high to allow clearing reset</i>
				1 <i>drv_otpw</i> 1: Indicates, that the driver temperature has exceeded overtemperature prewarning-level. No action is taken. This flag is latched.
				2 <i>drv_ot</i> 1: Indicates, that the driver has been shut down due to overtemperature. This flag can only be cleared when the temperature is below the limit again. It is latched for information. ORed to STATUS output.
				3 <i>uv_cp</i> 1: Indicates an undervoltage on the charge pump. The driver is disabled during undervoltage. This flag is latched for information. ORed to STATUS output.
				4 <i>shortdet_u</i> 1: U short counter has triggered at least once. ORed to STATUS output.

GENERAL CONFIGURATION REGISTERS (0x00...0x0F)				
R/W	Addr	n	Register	Description / bit names
				5 <i>s2gu</i> 1: Short to GND detected on phase U. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				6 <i>s2vsu</i> 1: Short to VS detected on phase U. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				7 -
				8 <i>shortdet_v</i> 1: V short counter has triggered at least once. ORed to STATUS output.
				9 <i>s2gv</i> 1: Short to GND detected on phase V. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				10 <i>s2vsv</i> 1: Short to VS detected on phase V. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				11 -
				12 <i>shortdet_w</i> 1: short counter has triggered at least once. ORed to STATUS output.
				13 <i>s2gw</i> 1: Short to GND detected on phase W. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				14 <i>s2vsw</i> 1: Short to VS detected on phase W. The driver becomes disabled until flag becomes cleared. ORed to STATUS output.
				<b>Bit</b> <b>INPUT</b>
				Reads the state of all input pins available
				0 UL
				1 UH
				2 VL
				3 VH
				4 WL
				5 WH
				6 DRV_EN
				7 0
				8 OTPW
				9 OT136°C
				10 OT143°C
				11 OT150°C
				31.. 24 <i>VERSION</i> : 0x10=first version of the IC Identical numbers mean full digital compatibility.
W	0x06		<i>OTP_PROG</i>	<b>Bit</b> <b>OTP_PROGRAM – OTP programming</b> Write access programs OTP memory (one bit at a time),

GENERAL CONFIGURATION REGISTERS (0x00...0x0F)				
R/W	Addr	n	Register	Description / bit names
				Read access refreshes read data from OTP after a write
				2..0 <i>OTPBIT</i> Selection of OTP bit to be programmed to the selected byte location (n=0..7: programs bit n to a logic 1)
				5..4 <i>OTPBYTE</i> Set to 00
				15..8 <i>OTPMAGIC</i> Set to 0xbd to enable programming. A programming time of minimum 10ms per bit is recommended (check by reading <i>OTP_READ</i> ).
R	0x07		<i>OTP_READ</i>	<b>Bit</b> <i>OTP_READ</i> (Access to OTP memory result and update) <i>See table 5.1.1!</i>
				7..0 <i>OTPO</i> byte 0 read data
RW	0x08	5	<i>FACTORY_CONF</i>	4..0 <i>FCLKTRIM</i> (Reset default: <i>OTP</i> ) 0..31: Lowest to highest clock frequency. Check at charge pump output. The frequency span is not guaranteed, but it is tested, that tuning to 12MHz internal clock is possible. The devices come preset to 12MHz clock frequency by OTP programming. (Reset Default: <i>OTP</i> )
				<b>Bit</b> <i>SHORT_CONF</i>
				3..0 <i>S2VS_LEVEL</i> : Short to VS detector level for lowside FETs. Checks for voltage drop in LS MOSFET and bottom shunt resistor. 1 (highest sensitivity) ... 15 (lowest sensitivity) (Reset Default: <i>OTP 6 or 12</i> )
				11..8 <i>S2G_LEVEL</i> : Short to GND detector level for highside FETs. Checks for voltage drop on high side MOSFET 2 (highest sensitivity) ... 15 (lowest sensitivity) <i>Hint: Use high setting. Tune S2VS level for more sensitive overcurrent detection.</i> (Reset Default: <i>OTP 6 or 12</i> )
RW	0x09	19	<i>SHORT_CONF</i>	17..16 <i>SHORTFILTER</i> : Spike filtering bandwidth for short detection 0 (lowest, 100ns), 1 (1µs), 2 (2µs) 3 (3µs) <i>Hint: Increase value, if erroneous short detection occurs.</i> (Reset Default = %01)
				20 <i>shortdelay</i> : Short detection delay 0=750ns: normal, 1=1500ns: high The short detection delay shall cover the bridge switching time. 0 will work for most applications. (Reset Default = 0)
				25..24 <i>RETRY</i> : Number of retries for short detection 0: Half bridge disabled after first short detection 1..3: Half bridge re-enabled in next chopper cycles 1 time to 3 times. With retry, the short-counter is decreased once each 256 chopper cycles per coil, unless the upper limit has been reached. (Reset Default = 3)



GENERAL CONFIGURATION REGISTERS (0x00...0x0F)				
R/W	Addr	n	Register	Description / bit names
				28 <i>protect_parallel</i> 0: Only the detected half bridge driver becomes shut down upon final short detection 1: All half bridge drivers become shut down upon final short detection (Reset Default = 1)
				29 <i>disable_S2G</i> 0: Short to GND (HS) protection enabled 1: No short to GND protection (Reset Default = 0)
				30 <i>disable_S2VS</i> 0: Short to VS (LS) protection enabled 1: No short to VS protection (Reset Default = 0)
				<b>Bit DRV_CONF</b>
				4..0 <i>BBMCLKS</i> : 0..15: Digital BBM time in clock cycles (typ. 42ns/CLK). <i>BBMCLKS</i> is used in combination with <i>singleline=1</i> . It is not applicable with individual LS and HS signals. (Reset Default: OTP 1..4)
				15:5 unused
				17..16 <i>OTSELECT</i> : Selection of over temperature level for bridge disable, switch on after cool down to 120°C / OTPW level. 00: 150°C (default) 01: 143°C 10: 136°C 11: 120°C (not recommended, no hysteresis)  <i>Hint: Adapt overtemperature threshold as required to protect the MOSFETs or other components on the PCB.</i> (Reset Default = %00)
				19..18 <i>DRVSTRENGTH</i> : Selection of gate driver current. Adapts the gate driver current to the gate charge of the external MOSFETs. 00: weak 01: weak+TC (medium above OTPW level) 10: medium 11: strong  <i>Hint: Choose the lowest setting giving slopes &lt;100ns.</i> (Reset Default = %10)
				31:20 unused
RW	0x0A	22	DRV_CONF	

### 5.1.1 OTP\_READ – OTP configuration memory

The OTP memory holds power up defaults for certain registers. All OTP memory bits are cleared to 0 by default. Programming only can set bits, clearing bits is not possible. Factory tuning of the clock frequency affects *otp0.0* to *otp0.4*. The state of these bits therefore may differ between individual ICs.

<b>0x05: OTP_READ – OTP MEMORY MAP</b>			
<b>Bit</b>	<b>Name</b>	<b>Function</b>	<b>Comment</b>
7	<i>otp0.7</i>	<i>otp_BBM</i>	Reset default for <i>BBM</i> 0: 4 clocks 1: 1 clocks 2: 2 clocks 3: 3 clocks
6	<i>otp0.6</i>		
5	<i>otp0.5</i>	<i>otp_S2_LEVEL</i>	Reset default for <i>Short detection Levels</i> : 0: <i>S2G_LEVEL</i> = <i>S2VS_LEVEL</i> = 6 1: <i>S2G_LEVEL</i> = <i>S2VS_LEVEL</i> = 12
4	<i>otp0.4</i>	<i>OTP_FCLKTRIM</i>	Reset default for <i>FCLKTRIM</i> 0: lowest frequency setting 31: highest frequency setting <i>Attention: This value is pre-programmed by factory clock trimming to the default clock frequency of 24MHz and differs between individual ICs! It should not be altered.</i>
3	<i>otp0.3</i>		
2	<i>otp0.2</i>		
1	<i>otp0.1</i>		
0	<i>otp0.0</i>		

## 6 Diagnostics and Protection

The TMC6100 supplies a complete set of diagnostic and protection capabilities, like short circuit protection and undervoltage detection. See the *DRV\_STATUS* table for details.

### 6.1 Temperature Sensors

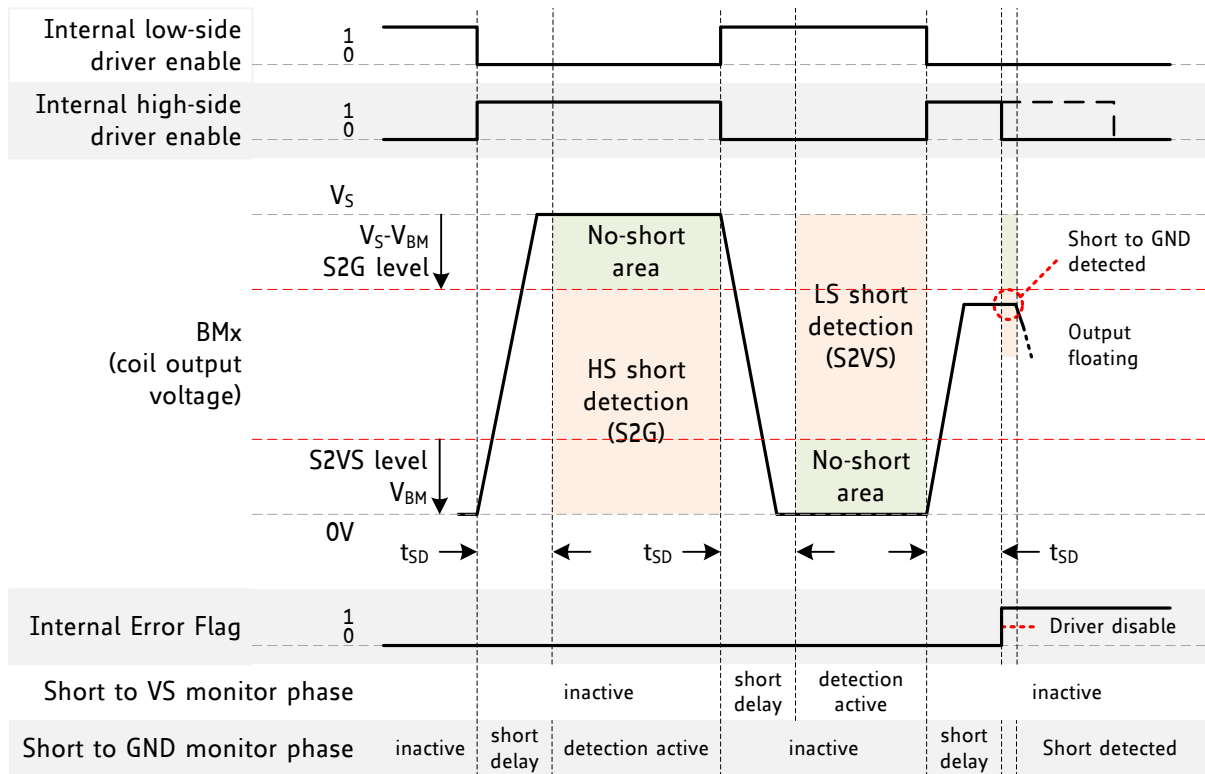
The driver integrates a four-level temperature sensor (120°C pre-warning and selectable 136°C / 143°C / 150°C thermal shutdown) for diagnostics and for protection of the IC and the power MOSFETs and adjacent components against excess heat. Choose the overtemperature level to safely cover error conditions like missing heat convection. Heat is mainly generated by the power MOSFETs, and, at increased voltage, by the internal voltage regulators. For many applications, already the overtemperature pre-warning will indicate an abnormal operation situation and can be used to initiate user warning or power reduction measures like motor current reduction. The thermal shutdown is just an emergency measure and temperature rising to the shutdown level should be prevented by design.

After triggering the overtemperature sensor (*ot* flag), the driver remains switched off until the system temperature falls below the pre-warning level (*otpw*) to avoid continuous heating to the shutdown level.

### 6.2 Short Protection

The TMC6100 protects the MOSFET power stages against a short circuit or overload condition by monitoring the voltage drop in the high-side MOSFETs, as well as the voltage drop in the low-side MOSFETs (Figure 6.1). A programmable short detection delay (*shortdelay*) allows adjusting the detector to work with very slow switching slopes. Additionally, the short detector allows filtering of the signal. This helps to prevent spurious triggering caused by effects of PCB layout, or long, adjacent motor cables (*SHORTFILTER*). All control bits are available via register *SHORT\_CONF*. Additionally, the short detection is protected against single events, e.g. caused by ESD discharges, by retrying up to three times before switching off the motor continuously (program in *SHORT\_CONF.RETRY*).

Parameter	Description	Setting	Comment
<i>S2VS_LEVEL</i>	Short or overcurrent detector level for lowside FETs. Checks for voltage drop in LS MOSFET and optional bottom shunt sense resistor. <i>Hint: May be tuned for sensitive detection.</i>	4...15	1 (highest sensitivity) ... 15 (lowest sensitivity) (Reset Default: OTP 6 / 12)
<i>S2G_LEVEL</i>	Short to GND detector level for highside FETs. Checks for voltage drop on high side MOSFET. <i>Hint: Use high setting to avoid false detection.</i>	2...15	2 (highest sensitivity) ... 15 (lowest sensitivity) (Reset Default: OTP 6 / 12)
<i>SHORT_FILTER</i>	Spike filtering bandwidth for short detection <i>Hint: Increase value, if erroneous short detection occurs.</i>	0...3	0 (lowest, 100ns), 1 (1µs) (Reset Default), 2 (2µs), 3 (3µs)
<i>RETRY</i>	Number of retries after short detection until permanent bridge shutdown	0...3	(Reset Default = 3)
<i>shortdelay</i>	<i>shortdelay</i> : Short detection delay The delay shall cover the bridge switching time.	0/1	0=750ns: normal, 1=1500ns: high
<i>disable_S2VS</i>	1: Disable short to VS protection.	0/1	Leave detection enabled for normal use (0).
<i>disable_S2G</i>	1: Disable short to GND protection.	0/1	Leave detection enabled for normal use (0).
<i>protectparallel</i>	0: Individual half bridge protection 1: Disable all bridges upon single half bridge short condition	0/1	(Reset Default = 1)



**Figure 6.1 Short detection (U, V or W output)**

As the low-side short detection includes a bottom shunt sense resistor (if applied), it can be set to a high sensitivity and provides good precision of current detection. This way, it will safely cover most overcurrent conditions, i.e. when the motor stalls, or is abruptly stopped in stealthChop mode.

Once a short condition is safely detected, the corresponding driver bridge (U, V or W) becomes switched off, and the corresponding *s2gu*, *s2gv* or *s2gw* flag, respectively *s2vsu*, *s2vsv* or *s2vsw* becomes set. Optionally, the complete bridge becomes switched off (set *protect\_parallel*). To restart the motor, disable and re-enable the driver.

**Attention:**  
Short protection cannot protect the system and the power stages for all possible short events, as a short event is rather undefined and a complex network of external components may be involved. Therefore, short circuits should basically be avoided.

**Hint**  
Fine tune low-side short detection threshold, in order to provide a sensitive overcurrent protection, e.g. to protect motor and power stage. The reproducibility mainly depends on production stray of the MOSFETs and is typically within +30%. To see any overcurrent pulse at the FAULT output, set flag *short\_direct*.  
Set a high value for high-side short protection, because detection is more subject to stray and inductive voltage drop on interconnections.

## 7 External Reset

The chip is loaded with default values during power on via its internal power-on reset. In order to reset the chip to power on defaults, any of the supply voltages monitored by internal reset circuitry (VSA, +5VOUT or VCC\_IO) must be cycled. As +5VOUT is the output of the internal voltage regulator, it cannot be cycled via an external source except by cycling VSA. It is easiest and safest to cycle VCC\_IO in order to completely reset the chip. Also, current consumed from VCC\_IO is low and therefore it has simple driving requirements. Due to the input protection diodes not allowing the digital inputs to rise above VCC\_IO level, all inputs must be driven low during this reset operation. When this is not possible, an input protection resistor may be used to limit current flowing into the related inputs.

## 8 Clock Oscillator and Input

The clock is the timing reference for the internal BBM time generator and is used to operate the SPI interface. The factory-trimmed on-chip clock oscillator provides timing which is sufficient for most use cases.

### 8.1 Using the Internal Clock

Directly tie the CLK input to GND near to the IC if the internal clock oscillator is to be used. It provides a precision of roughly  $\pm 4\%$ , which is precise enough for BBM operation.

### 8.2 Using an External Clock

When an external clock is available, a frequency of 4 MHz to 13.4 MHz is possible (max. 16MHz with 50% dutycycle). Especially with low clock frequency, make sure, that the SPI timing is kept in order to ensure proper SPI operation. Make sure, that the clock source supplies clean CMOS output logic levels and steep slopes when using a high clock frequency. The external clock input is enabled with the second positive polarity seen on the CLK input.

#### *Attention*

Switching off the external clock frequency prevents the driver from operating normally. Therefore, an internal watchdog switches back to internal clock in case the external signal is missing for more than roughly 32 internal clock cycles.

#### 8.2.1 Considerations on the Frequency

A higher frequency allows more precise BBM timing and faster SPI operation. A lower frequency will reduce power consumption of the IC, which especially at high VSA supply voltages reduces overall power consumption by a few 100mW. However, the internal timing should be sufficient for most applications. Take into account, that the input signals are synchronized to the clock, in case internal BBM generation becomes used.

## 9 Absolute Maximum Ratings

The maximum ratings may not be exceeded under any circumstances. Operating the circuit at or near more than one maximum rating at a time for extended periods shall be avoided by application design.

Parameter	Symbol	Min	Max	Unit
Supply voltage operating with inductive load	$V_{VS}, V_{VSA}$	-0.5	65	V
Supply and bridge voltage short time peak (limited by peak voltage on charge pump output and Cxx pins*)	$V_{VSMAX}$		70	V
VSA supply voltage	$V_{VSAMAX}$	-0.5	65	V
Peak voltages on Cxx bootstrap pins and VCP	$V_{CXCXCP}$		85	V
Supply voltage V12	$V_{12VOUT}$	-0.5	15	V
Peak voltages on U/V/W pins (due to stray inductivity)	$V_X$	-6	$V_{VS}+6$	V
Peak voltages on Cxx bootstrap pins relative to BM	$V_{CXX}$	-0.5	16	V
I/O supply voltage	$V_{VIO}$	-0.5	5.5	V
Supply voltage (5VOUT)	$V_{5VOUT}$	-0.5	5.5	V
Logic input voltage	$V_I$	-0.5	$V_{VIO}+0.5$	V
Maximum current to / from digital pins and low voltage I/Os (short time peak current)	$I_{IO}$		+/-500	mA
5V regulator output current (internal plus external load)	$I_{5VOUT}$		30	mA
5V regulator continuous power dissipation ( $(V_{VSA}-5V) * I_{5VOUT}$ )	$P_{5VOUT}$		1	W
12V regulator output current (internal plus external load)	$I_{12VOUT}$		20	mA
12V regulator continuous power dissipation ( $(V_{VM}-5V) * I_{5VOUT}$ )	$P_{12VOUT}$		0.5	W
Junction temperature	$T_J$	-50	150	°C
Storage temperature	$T_{STG}$	-55	150	°C
ESD-Protection for interface pins (Human body model, HBM)	$V_{ESDAP}$		4	kV
ESD-Protection for handling (Human body model, HBM)	$V_{ESD}$		1	kV

\*) Stray inductivity of power routing will lead to ringing of the supply voltage when driving an inductive load. This ringing results from the fast switching slopes of the driver outputs in combination with reverse recovery of the body diodes of the output driver MOSFETs. Even small trace inductivities as well as stray inductivity can easily generate a few volts of ringing leading to temporary voltage overshoot. This should be considered when working near the maximum voltage.

## 10 Electrical Characteristics

### 10.1 Operational Range

Parameter	Symbol	Min	Max	Unit
Junction temperature	$T_J$	-40	125	°C
Supply voltage for motor and bridge	$V_{VS}$	10	60	V
Supply voltage VSA	$V_{VSA}$	10	60	V
Supply voltage for VSA and 12OUT (internal gate voltage regulator bridged)	$V_{12VOUT}, V_{VSA}$	10	13	V
Lower Supply voltage (reduced spec, short to GND protection not functional), lower limit depending on MOSFETs gate threshold voltage and load current	$V_{VS}$	8		V
I/O supply voltage	$V_{VIO}$	3.00	5.25	V

## 10.2 DC and Timing Characteristics

DC characteristics contain the spread of values guaranteed within the specified supply voltage range unless otherwise specified. Typical values represent the average value of all parts measured at +25°C. Temperature variation also causes stray to some values. A device with typical values will not leave Min/Max range within the full temperature range.

Power Supply Current		DC-Characteristics				
		$V_{VS} = V_{VSA} = 24.0V$				
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Total supply current, driver disabled $I_{VS} + I_{VSA}$	$I_S$	internal clock		10	15	mA
VSA supply current (VS and VSA separated)	$I_{VSA}$	$f_{CLK}=24MHz$ / internal clock, driver disabled		7		mA
Internal current consumption from 5V supply on VCC pin	$I_{VCC}$	GCONF.6='1'		5		mA
IO supply current (typ. at 5V)	$I_{VIO}$	no load on outputs, inputs at $V_{IO}$ or GND Excludes pullup / pull-down resistors		15	30	$\mu A$

Motor Driver		DC- and Timing-Characteristics				
		$V_{VS} = 24.0V$ ; $T_j=50^\circ C$				
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
RDS <sub>ON</sub> lowside off driver	$R_{ONL}$	Gate off		1.0	1.6	$\Omega$
RDS <sub>ON</sub> highside off driver	$R_{ONH}$	Gate off		1.3	2.0	$\Omega$
Gate drive current low side MOSFET turning on at 2V $V_{GS}$	$I_{SLPON0}$	DRIVESTRENGTH=0		400		mA
	$I_{SLPON2}$	DRIVESTRENGTH=2		800		mA
	$I_{SLPON3}$	DRIVESTRENGTH=3		1200		mA
Gate drive current high side MOSFET turning on at 2V $V_{GS}$	$I_{SLPON0}$	DRIVESTRENGTH=0		400		mA
	$I_{SLPON2}$	DRIVESTRENGTH=2		800		mA
	$I_{SLPON3}$	DRIVESTRENGTH=3		1200		mA
Gate drive current low side MOSFET turning off at 4V $V_{GS}$	$I_{SLPOFF0}$	DRIVESTRENGTH=0		600		mA
	$I_{SLPOFF2}$	DRIVESTRENGTH=2		1200		mA
	$I_{SLPOFF3}$	DRIVESTRENGTH=3		1800		mA
Gate drive current high side MOSFET turning on at 4V $V_{GS}$	$I_{SLPOFF0}$	DRIVESTRENGTH=0		600		mA
	$I_{SLPOFF2}$	DRIVESTRENGTH=2		1200		mA
	$I_{SLPOFF3}$	DRIVESTRENGTH=3		1800		mA
Minimum effective BBM time enforced in individual or singleline mode	$t_{BBM0}$	Individual LS and HS signals ( <i>singleline=0</i> )	30	50	70	ns
Reaction delay time LS/HS input signal change to start of gate driver output change	$t_{DLY}$	Individual LS and HS signals ( <i>singleline=0</i> )	65	85	110	ns
Matching difference of gate driver reaction delay times	$t_{DLYMATCH}$	Individual LS and HS signals ( <i>singleline=0</i> )			10	ns

Charge Pump		DC-Characteristics				
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Charge pump output voltage	$V_{VCP-V_{VS}}$	operating	$V_{12VOUT} - 2$	$V_{12VOUT} - 1$		V
Charge pump voltage threshold for undervoltage detection	$V_{VCP-V_{VS}}$	rising, using internal 5V regulator voltage	4.5	5.5	6.5	V
Charge pump frequency	$f_{CP}$			$1/32 f_{CLKOSC}$		

Linear Regulator		DC-Characteristics				
$V_{VS} = V_{VSA} = 24.0V$						
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	$V_{5VOUT}$	$T_J = 25^\circ C$	4.80	5.0	5.20	V
Deviation of output voltage over the full temperature range	$V_{5VOUT(DEV)}$	drivers disabled $T_J = \text{full range}$		+/-5	+/-50	mV
Deviation of output voltage over the supply voltage	$V_{5VOUT(DEV)}$	drivers disabled, internal clock $T_A = 25^\circ C$ $V_{VSA} = 10V \text{ to } 30V$			+/-20	mV / 10V
Output voltage	$V_{12VOUT}$	operating, internal clock $T_J = 25^\circ C$	10.8	11.5	12.2	V

Clock Oscillator and Input		Timing-Characteristics				
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Clock oscillator frequency (factory calibrated)	$f_{CLKOSC}$	$t_j = -50^\circ C$		23.4		MHz
	$f_{CLKOSC}$	$t_j = 50^\circ C$	23	24.0	25	MHz
	$f_{CLKOSC}$	$t_j = 150^\circ C$		24.2		MHz
External clock frequency (operating)	$f_{CLK}$	40%..60% dutycycle for typ. 50% for max.	4	10-13.4	16	MHz
External clock high / low level time	$t_{CLKH} / t_{CLKL}$	CLK driven to $0.1 V_{VIO} / 0.9 V_{VIO}$	10			ns
External clock timeout detection in cycles of internal $f_{CLKOSC}$	$t_{CLKH1}$	CLK driven high	32		48	cycles $f_{CLKOSC}$



Short Detection	DC-Characteristics					
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Short to GND / Short to VS detector delay (Start of gate switch on to short detected) Including 100ns filtering time	$t_{SD0}$	<i>FILT_ISENSE=0</i> <i>S2xx_LEVEL=6</i> <i>shortdelay=0</i>	0.5	0.85	1.1	$\mu$ s
	$t_{SD1}$	<i>shortdelay=1</i>	1.1	1.6	2.2	$\mu$ s
Short detector level S2VS (measurement includes drop in bottom shunt)	$V_{BM}$	<i>S2VS_LEVEL=15</i>	1.4	1.56	1.72	V
		<i>S2VS_LEVEL=6</i>	0.55	0.625	0.70	V
Short detector level S2G	$V_S - V_{BM}$	<i>S2G_LEVEL=15</i> <i>VS&lt;52V</i>	1.3	1.56	1.85	V
		<i>S2G_LEVEL=15</i> <i>VS&lt;60V</i>	1.0			V
		<i>S2G_LEVEL=6</i> <i>VS&lt;52V</i>	0.46	0.625	0.85	V
		<i>S2G_LEVEL=6</i> <i>VS&lt;60V</i>	0.20			V

Detector Levels	DC-Characteristics					
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
$V_{VSA}$ undervoltage threshold for RESET	$V_{UV\_VSA}$	$V_{VSA}$ rising	3.8	4.2	4.6	V
$V_{SVOUT}$ undervoltage threshold for RESET	$V_{UV\_SVOUT}$	$V_{SVOUT}$ rising		3.5		V
$V_{VCC\_IO}$ undervoltage threshold for RESET	$V_{UV\_VIO}$	$V_{VCC\_IO}$ rising (delay typ. 10 $\mu$ s)	2.0	2.2	3.0	V
$V_{VCC\_IO}$ undervoltage detector hysteresis	$V_{UV\_VIOHYST}$			0.3		V
Overtemperature prewarning 120°C	$T_{OTPW}$	Temperature rising	100	120	140	°C
Overtemperature shutdown 136 °C	$T_{OT136}$	Temperature rising		136		°C
Overtemperature shutdown 143 °C	$T_{OT143}$	Temperature rising		143		°C
Overtemperature shutdown 150 °C	$T_{OT150}$	Temperature rising	135	150	170	°C

Digital pins	DC-Characteristics					
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage low level	$V_{INLO}$		-0.3		$0.3 V_{VIO}$	V
Input voltage high level	$V_{INHI}$		$0.7 V_{VIO}$		$V_{VIO}+0.3$	V
Input Schmitt trigger hysteresis	$V_{INHYST}$			$0.12 V_{VIO}$		V
Output voltage low level	$V_{OUTLO}$	$I_{OUTLO} = 2mA$			0.2	V
Output voltage high level	$V_{OUTH}$	$I_{OUTH} = -2mA$	$V_{VIO}-0.2$			V
Input leakage current	$I_{LEAK}$		-10		10	$\mu A$
Pullup / pull-down resistors	$R_{PU}/R_{PD}$		132	166	200	k $\Omega$
Digital pin capacitance	C			3.5		pF

### 10.3 Thermal Characteristics

The following table shall give an idea on the thermal resistance of the package. The thermal resistance for a four-layer board will provide a good idea on a typical application. Actual thermal characteristics will depend on the PCB layout, PCB type and PCB size. The thermal resistance will benefit from thicker CU (inner) layers for spreading heat horizontally within the PCB. Also, air flow will reduce thermal resistance.

Parameter	Symbol	Conditions	Typ	Unit
Typical power dissipation	$P_D$	20kHz chopper, 24V supply, internal supply regulators	<0.5	W
Thermal resistance junction to ambient on a multilayer board	$R_{TMJA}$	Dual signal and two internal power plane board (2s2p) as defined in JEDEC EIA JESD51-5 and JESD51-7 (FR4, 35 $\mu m$ CU, 70mm x 133mm, d=1.5mm)	21	K/W
Thermal resistance junction to board	$R_{TJB}$	PCB temperature measured within 1mm distance to the package leads	8	K/W
Thermal resistance junction to case	$R_{TJC}$	Junction temperature to heat slug of package	3	K/W

**Table 10.1 Thermal characteristics QFN7x7-EP**

The thermal resistance in an actual layout can be tested by checking for the heat up caused by the standby power consumption of the chip. When no motor is attached, all power seen on the power supply is dissipated within the chip.

## 11 Layout Considerations

### 11.1 Exposed Die Pad

The TMC6100 uses its die attach pad to dissipate heat from the gate drivers and the linear regulator to the board. For best electrical and thermal performance, use a reasonable amount of solid, thermally conducting vias between the die attach pad and the ground plane. The printed circuit board should have a solid ground plane spreading heat into the board and providing for a stable GND reference.

### 11.2 Wiring GND

All signals of the TMC6100 are referenced to their respective GND. Directly connect all GND pins under the device to a common ground area (GND, GNDP, GNDA and die attach pad). The GND plane right below the die attach pad should be treated as a virtual star point. For thermal reasons, the PCB top layer shall be connected to a large PCB GND plane spreading heat within the PCB.

*Attention*

Place the TMC6100 near to the MOSFET bridge in order to avoid ringing leading to GND differences.

### 11.3 Wiring Bridge Supply

The power bridge will draw the full coil current in pulses with extremely high  $dI/dt$ . Thus, any inductivity between VS supply filtering and the MOSFETs can lead to severe voltage spikes. This has to be avoided. Avoid any bend in the supply traces between filtering capacitors and MOSFET switches, and keep distance as small as possible. Especially for high current, use a separate plane for the supply voltage, and a sufficient number and capacity for supply filtering. Use an additional capacitor for the IC VS pin, as additional ripple voltage would cause severe current spikes on the charge pump capacitor. A tiny series resistor can be added to avoid this.

*Attention*

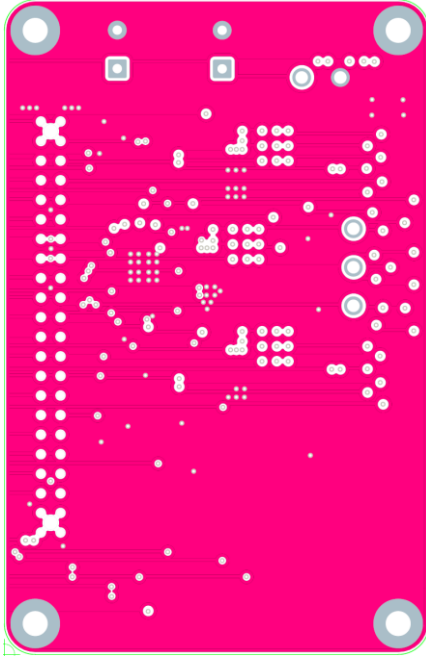
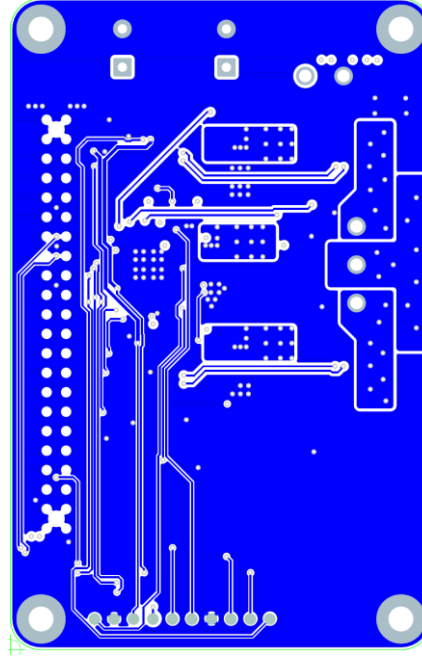
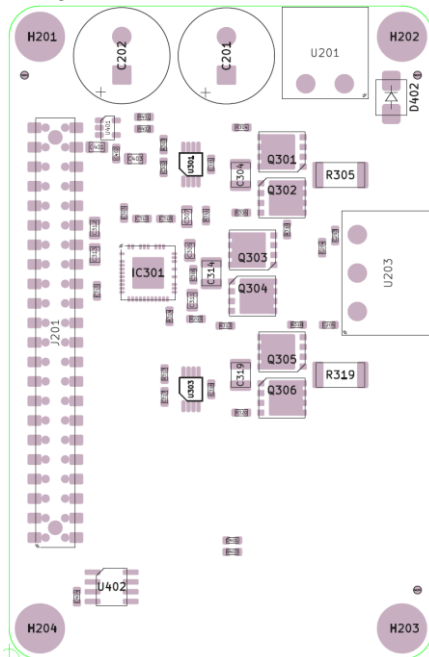
Keep supply voltage ripple low, by using sufficient filtering capacity close to the MOSFET bridge.

### 11.4 Supply Filtering

The 5VOUT output voltage ceramic filtering capacitor (2.2 to 4.7  $\mu$ F recommended) should be placed as close as possible to the 5VOUT pin, with its GND return going directly to the GNDA pin. This ground connection shall not be shared with other loads or additional vias to the GND plane. Use as short and as thick connections as possible. A 100 nF or larger filtering capacitor should be placed as closely as possible to the VSA pin to ground plane. Provide sufficient filtering capacity near the power bridge MOSFETs, in order to avoid ringing following each switching event. Make sure, that VS does not see excessive voltage spikes caused by bridge operation and place a 100 nF or larger filter capacitor to GND close to the VS pin.

Please carefully read chapters 3.4 and 3.5 to understand the special considerations with regard to layout and component selection for the external MOSFET power bridges.



**3- Inner Layer (supply VS)****4- Bottom Layer****Components****Figure 11.1 Layout example**

Please refer [www.trinamic.com](http://www.trinamic.com) for complete schematic and layout data of the evaluation board.

## 12 Package Mechanical Data

### 12.1 Dimensional Drawings QFN7x7-EP

Attention: Drawings not to scale.

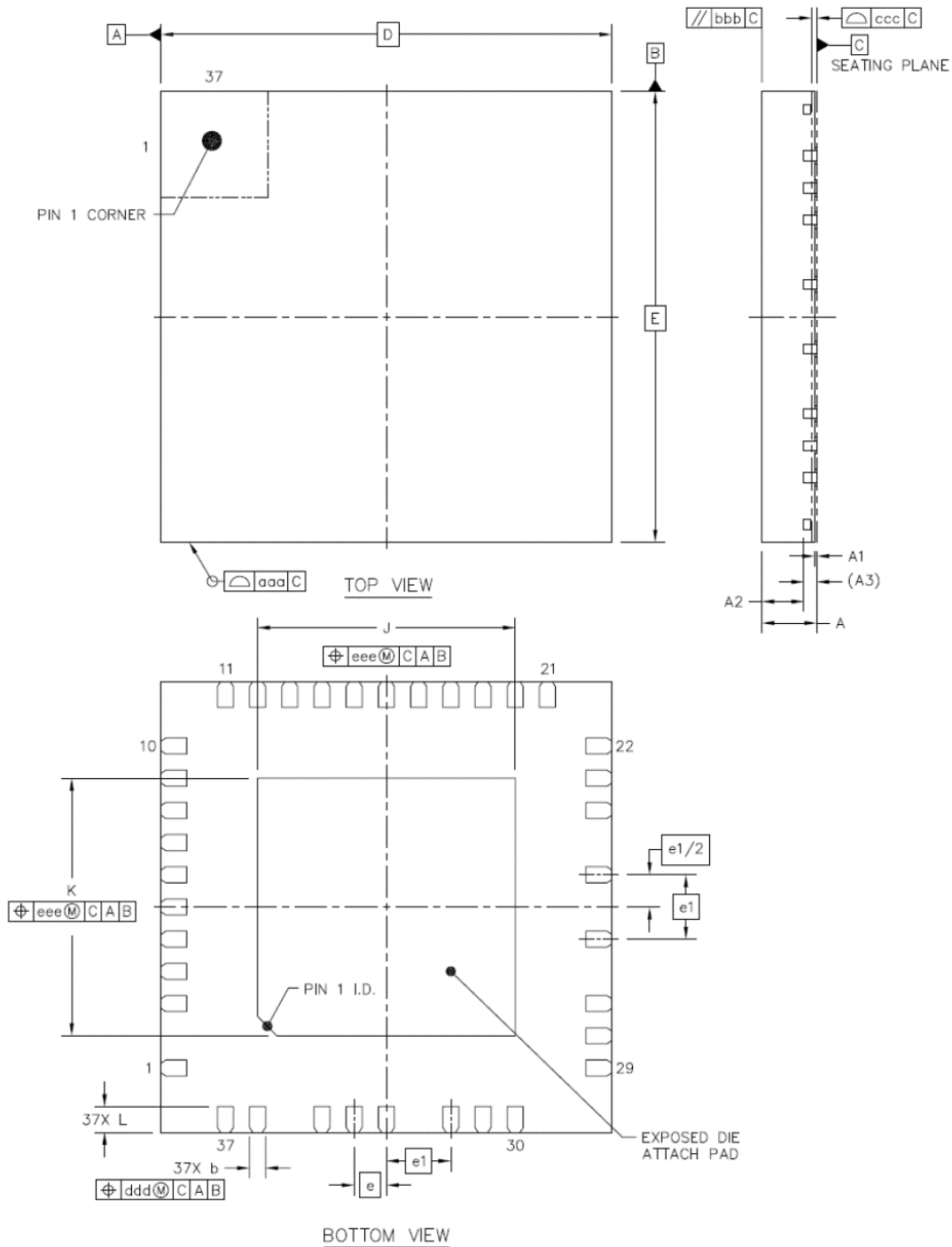


Figure 12.1 Dimensional drawings QFN7x7

Parameter	Ref	Min	Nom	Max
total thickness	A	0.8	0.85	0.9
stand off	A1	0	0.035	0.05
mold thickness	A2	-	0.65	-
L/F thickness	A3	0.203 REF		
lead width	b	0.2	0.25	0.3
body size X	D	7.0 BSC		
body size Y	E	7.0 BSC		
lead pitch	e	0.5 BSC		
lead pitch (wide)	e1	1.0 BSC		
exposed die pad size X	J	3.9	4	4.1
exposed die pad size Y	K	3.9	4	4.1
lead length	L	0.35	0.4	0.45
package edge tolerance	aaa			0.1
mold flatness	bbb			0.1
coplanarity	ccc			0.08
lead offset	ddd			0.1
exposed pad offset	eee			0.1

## 12.2 Package Codes

Type	Package	Temperature range	Code & marking	MSL level
TMC6100-LA	QFN7x7-EP (RoHS)	-40°C ... +125°C	TMC6100LA	MSL 3 / 160h
TMC6100-LA-T	Tape on reel packed products			

## 13 Disclaimer

TRINAMIC Motion Control GmbH & Co. KG does not authorize or warrant any of its products for use in life support systems, without the specific written consent of TRINAMIC Motion Control GmbH & Co. KG. Life support systems are equipment intended to support or sustain life, and whose failure to perform, when properly used in accordance with instructions provided, can be reasonably expected to result in personal injury or death.

Information given in this data sheet is believed to be accurate and reliable. However no responsibility is assumed for the consequences of its use nor for any infringement of patents or other rights of third parties which may result from its use.

Specifications are subject to change without notice.

All trademarks used are property of their respective owners.

## 14 ESD Sensitive Device

The TMC6100 is an ESD sensitive CMOS device sensitive to electrostatic discharge. Take special care to use adequate grounding of personnel and machines in manual handling. After soldering the devices to the board, ESD requirements are more relaxed. Failure to do so can result in defect or decreased reliability.



## 15 Designed for Sustainability

Sustainable growth is one of the most important and urgent challenges today. We at Trinamic try to contribute by designing highly efficient IC products, to minimize energy consumption, ensure best customer experience and long-term satisfaction by smooth and silent run, while minimizing the demand for external resources, e.g. for power supply, cooling infrastructure, reduced motor size and magnet material by intelligent control interfaces and advanced algorithms.

Please help and design efficient and durable products made for a sustainable world.



## 16 Table of Figures

FIGURE 1.1 STANDALONE APPLICATION .....	4
FIGURE 1.2 STANDALONE APPLICATION USING SINGLE SHUNT CURRENT SENSING .....	5
FIGURE 1.3 SPI MODE CONFIGURATION.....	5
FIGURE 2.1 TMC6100-LA PINNING QFN 37 SPECIAL (7X7MM <sup>2</sup> ).....	7
FIGURE 3.1 STANDARD APPLICATION CIRCUIT.....	10
FIGURE 3.2 EXTERNAL GATE VOLTAGE SUPPLY.....	11
FIGURE 3.3 STANDBY SWITCH .....	12
FIGURE 3.4 MILLER CHARGE DETERMINES SWITCHING SLOPE .....	13
FIGURE 3.5 SLOPES, MILLER PLATEAU AND BLANK TIME (BMx=U V OR W OUTPUT) .....	14
FIGURE 3.6 BRIDGE PROTECTION OPTIONS FOR POWER ROUTING INDUCTIVITY.....	15
FIGURE 3.7 RINGING OF OUTPUT (GREEN) AND GATE VOLTAGES (YELLOW, BLUE) WITH DRVSTRENGTH=0.....	16
FIGURE 3.8 RINGING OF OUTPUT (GREEN) AND GATE VOLTAGES (YELLOW, BLUE) WITH DRVSTRENGTH=2.....	16
FIGURE 3.9 RINGING OF OUTPUT (GREEN) AND GATE VOLTAGES (YELLOW, BLUE) WITH DRVSTRENGTH=3.....	16
FIGURE 3.10 DIODES FOR SAFE OFF CONDITION WITH HIGH GATE SERIES RESISTANCE .....	17
FIGURE 4.1 SPI TIMING.....	20
FIGURE 7.1 SHORT DETECTION (U, V OR W OUTPUT) .....	28
FIGURE 12.1 LAYOUT EXAMPLE .....	37
FIGURE 13.1 DIMENSIONAL DRAWINGS QFN7X7 .....	38

## 17 Revision History

Version	Date	Author BD= Bernhard Dwersteg	Description
V1.00	2019-NOV-14	BD	First version of Datasheet
V1.01	2020-JUN-10	BD	Updated logo

Table 17.1 Document Revisions